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## NEW INPUT MEMORY

A part of the electronic model for tides and storm surges

S. Ishiguro

1979

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#### ABSTRACT

In the electronic model for tides and storm surges, input data representing meteorological conditions (e.g. atmospheric-pressure field and wind field) for a certain period is stored in the memory first. Then the data is fed into each grid of the model simultaneously, with the electronic smoothing of time-increments in the data. Unlike a conventional numerical model, the whole dynamic computation is carried out without step-by-step procedures so that the differential (not difference) equations are solved.

This paper describes an electronic memory system for such a purpose. The main part of the system consists of N-channel MOS RAMs in large-scale integrated circuits, with DACs at the last stage, and control circuits. The system has a single 8-bit parallel input, and 144 channels of analogue opto-electronic outputs each of which can produce different functions simultaneously.

The input data can take either the form of  $F_1(t)_{x,y}$  or  $F_2(x,y)_t$ , but the outputs are always in the form of  $F_0(t)_{x,y}$ ; where x and y represent a position in the sea and t represents time. The conversion of the forms is carried out by the control circuits during the input-data feeding.

The system has enough capacity to handle the 100 km meteorological grids covering the seas around the British Isles, and to feed the meteorological input into the 'sea grids' several of which are contained in each meteorological grid. The system can store the hourly input data for 10 days which is sufficient for most storm surge analyses. The full data feeding takes about one minute with an optical tape-reader. The output data can be repeatedly produced with a typical period of 10 milli seconds which is enough to solve all the equations.

The system can also produce tidal components for the model, and has also been designed to be usable as a random access memory for conventional digital data having about 36K addresses.

The system is contained in a cabinet of  $50 \times 35 \times 22$  cm³, with a power supply cabinet having the same dimensions. The AC power supply input requires about 156W.

This paper has been written to describe the design and performance of the input memory system, and also as a guide to its operation and servicing.

#### 1. INTRODUCTION

The 'electronic model for tides and storm surges' (Ref. 1) contains an 'input memory'. This is a system by which a set of input data (e.g. atmospheric pressure data) is stored before it is fed into the main computation circuit in the model. Fig. 1 shows the position of the input memory in the model.

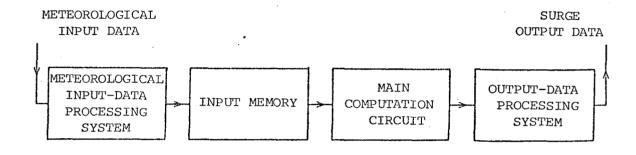


Fig. 1 Input memory in the electronic model for tides and storm surges (a greatly simplified illustration).

The main requirements for the input memory are:-

- To store a set of input data (about 200K bits in a digital form) for a certain period (say 10 milli seconds minimum, and 1 hour maximum);
- 2. To generate a set of simultaneous analogue current outputs (different waveforms in say 140 channels to drive up to 600 optoelectronic couplers); and
- 3. To rearrange the input data into a suitable form for the model, in a minimum time (ideally during the input-data feeding).

The most particular requirement, compared with a conventional memory, is  $\underline{2}$ , while  $\underline{1}$  and  $\underline{3}$  are not unusual. It is more economical, therefore, to construct a memory for the required conditions rather than to modify a standard memory.

In an earlier design, an optoelectronic-mechanical system was used for the input memory. Since 1972, a totally electronic system had been used successfully (Ref. 2), until an accident near the end of 1978 (a high voltage line touched the power supply line of the memory). On this occasion, it was decided to redesign the input memory using more up-to-date components and techniques, although the alterations to its interface circuits and physical construction were minimized. This paper describes the design and performance of the new input memory. A guide to its operation and servicing is also included.

Table 1 shows a comparison of the new and previous input memories. The main improvements to the new input memory are the increase of resolution in a waveform representation; the increase of store capacity; and the capability of a random data treatment (the memory can now be used as a general purpose data store within the system). The power supply for the new input memory has also been improved electronically and physically, with a more elaborate circuit protection facility.

The true cost of the new input memory is lower than the previous memory, considering the value of money. This is due to the use of large-scale integrated circuits which are mass-produced for micro-processors.

Table 1 Main improvements of the new memory over the previous memory.

		New memory	Previous memory	
Resolut	ion (bits/value)	8	6	
Time increments (per channel)		256	200	
Total memory bits  Digital output terminals		295K	168K	
		Data bus	Not available	
General-purpose data- handling capability		Random and sequential	Sequential only	
Memory type		N-channel MOS LSI RAM	CMOS SSR	
Waveform	monitor output	2V pk-pk	200mV pk-pk	
Main clock		Internal, 10 MHz	External, 10 kHz	
	For digital	+5V	+5v, -5v, -12v	
	For analogue	+12V, -12V	+12V, -12V, -1.5V	
Power	Regulator	Switching type & linear type	Linear type	
supply	Cooling	Natural convection	Motor fans	
	Total AC input power	165W	250W	
	Case dimensions	50 × 35 × 22 cm <sup>3</sup>	$50 \times 70 \times 22 \text{ cm}^3$	
Circuit protections		<u>a</u> High dc-voltage shut down (100ns)	Power-supply protections only	
		b 240V ac-line shut down (50ms)		
		<u>c</u> Audible alarm		
		d Power-supply protections		

#### 2. FUNDAMENTAL DESIGN

#### 2.1 Data rearrangements

Fig. 2 shows the timing diagram of the main data rearrangements. Data can be processed in five different modes:-

Sequential write mode 1
Sequential write mode 2
Sequential read mode 0
Sequential read mode 1
Random write/read mode

Sequential write mode 1 has been prepared to write the following set of data.

where x (t<sub>m</sub>) represents a value for station x and at time t<sub>m</sub>. The data is fed into the system in this order, but all the values related to x are written in channel n of the memory, keeping the order of t<sub>m</sub> within each section.

Sequential write mode 2 has been prepared to write the following set of data.

where  $x_n$  (t<sub>m</sub>) has the same definition as in the previous example. The data is fed into the system in this order, and all the data related to  $x_n$  is written in channel n of the memory, keeping the order within each set.

 $\mathbf{y}_{\mathrm{n}}(\mathbf{t}_{\mathrm{m}})$  is treated in the same way as above examples.

Note: When the writing has been completed, the written data by modes 1 and 2 become the same in the memory.

The actual data is a vector quantity, and the other component

Sequential read mode 0 has been prepared to read the data written in all the channels of the memory simultaneously, keeping synchronized so that all the values related to t are read at the same time. Values within each channel are read in the order of  $t_0$ ,  $t_1$ ,  $t_2$  ....  $t_{255}$ . The reading is automatically cycled without a break.

Sequential read mode 1 is similar to mode 0, but with intervals having a period equivalent to 256 increments.

Random write/read mode is a conventional arrangement. Each value of data is written in a particular address which is specified by an address code. The written data is read by giving the appropriate address code.

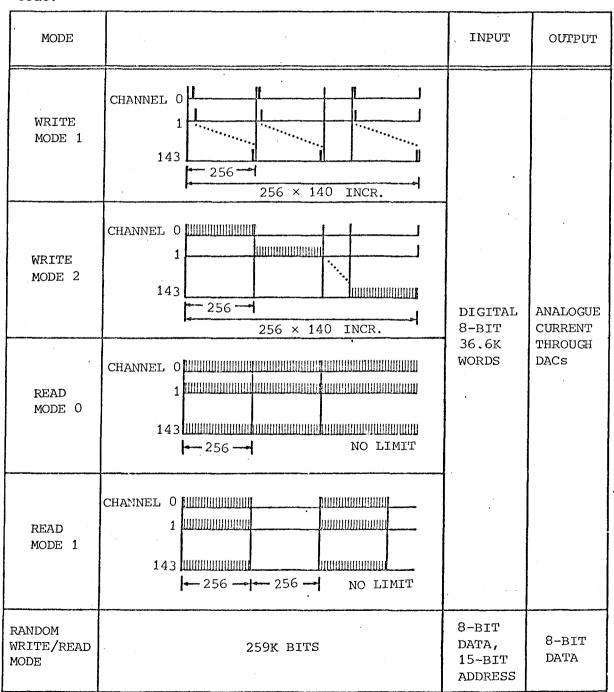


Fig. 2 Five modes of data rearrangement by the input memory.

## 2.2 System structure

Fig. 3 shows the fundamental structure of the input memory system. This consists of:-

Memory units (144 channel identical),
Address bus and data bus with switching circuits,
Sequential-code generator,
Data/address separator, and
Control circuit with a clock.

The input to the system is always digital (bit-parallel and word-serial), but the output of the system is digital (the same form as the input) and analogue (simultaneous reading of all the channels).

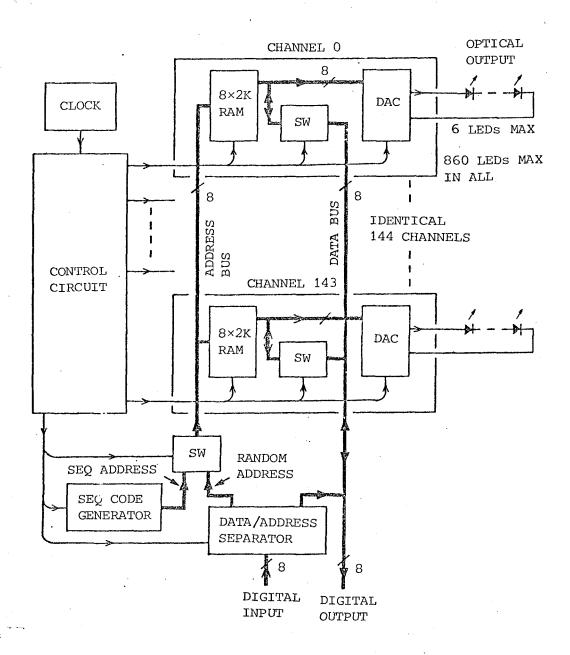


Fig. 3 Fundamental structure of the input memory system.

A set of data and their addresses, if any, are fed into the same input terminals of the system. If an input is random, with addresses, the data and addresses are separated by the data/address separator, and fed into the data bus and address bus respectively. If an input is sequential, without addresses, the data is fed directly (by-passing the data/address separator) into the data bus. In this case, their addresses are internally generated by the address generator following the order of arrival of each value in the data, and fed into the address bus.

Each memory channel consists of a  $2K \times 8$  RAM, a set of switches and a DAC. In a write mode, the switches are closed so that the input data is fed into both the RAM and DAC. The address codes enter into all the RAMs in the system simultaneously. However, the control circuit works so that only one address accepts an input value at a time. Since all the DACs are connected to the data bus in a write mode, the input data can be monitored in an analogue form through the DACs.

In a read mode, all switches in the memory channel are opened so that the written data in each RAM can only be fed into each DAC (note, the data written in each DAC is different). Each DAC drives up to 6 units of LEDs contained in optoelectronic couplers.

## 2.3 Fundamental circuit arrangements for the 5 modes

The system works in five different modes of operation (listed in 2.1) according to the control circuit. The fundamental circuit arrangement for each mode is shown in Figs. 4 to 7\*. Throughout these figures, essential control circuits only are shown for simplicity.

Each RAM chip has a chip-enable terminal  $(\overline{CE})$  and read/write control terminal (R/W), other than data terminals and address terminals. The five different modes of operation can be obtained by using different combinations of  $\overline{CE}$  and R/W, with respect to timing and chips concerned (280 units in all).

The start and end of any write mode is programmed by special codes on an input tape, and any read mode follows automatically, immediately after the completion of a write operation. The choice of one of the write modes, and the choice of one of the read modes, are carried out manually by selecting the control switches.

The write clock, in any write mode, enters from an external system (e.g. a tape reader) and is synchronized with a data entry. The read clock, in any sequential mode, is generated by an internal clock. The read clock in a random mode can be chosen either from an external or internal source.

<sup>\*</sup>Common symbols are used for ICs in Figs. 4 to 7 and Fig. 10 (the circuit diagram in chapter 3). For example, 93(3) indicates IC type 7493, and package no. 3 within the same type. If only one type of IC is used in the system, package no. is omitted. Also 93(3)/7 indicates pin no. 7 in the same package.

## Sequential write mode 1 (Fig. 4)

Three code generators are used in this mode.

The 1st code generator consists of 93(3). This is driven directly by the write clock, and generates 16 different 4-bit codes sequentially (one code per clock pulse). This output is fed into channel selectors 154(1) to 154(9) so that one channel of each selector is selected at a time. Only one channel throughout all the 154s can be selected, when the CE terminal of a particular 154 is activated at the same time.

The 2nd code generator consists of 93(4). This is driven by the 16th code output of 93(3), and generates 9 different 4-bit codes sequentially (one code per 16 clock pulses). This output is fed into another channel selector, 42, so that one channel of this selector is activated at a time. The combined effect of the 1st and 2nd code generators activates only one output terminal throughout all the 154s (144 terminals in all).

The 3rd code generator consists of 93(1) and 93(2). This is driven by the 141th output of the 154s, and generates 256 different 8-bit codes sequentially (one code per 140 clock pulses). This output is fed into the address bus to which all the RAMs are connected (140 sets in all). The combined effect of this output and the output of the 154s selects only one address throughout all the RAMs at a time, and this is activated by a clock pulse through a delay circuit and the R/W terminal.

The 11th output of 42 is used for driving 93(1) and 93(2), and for resetting 93(3) and 93(4).

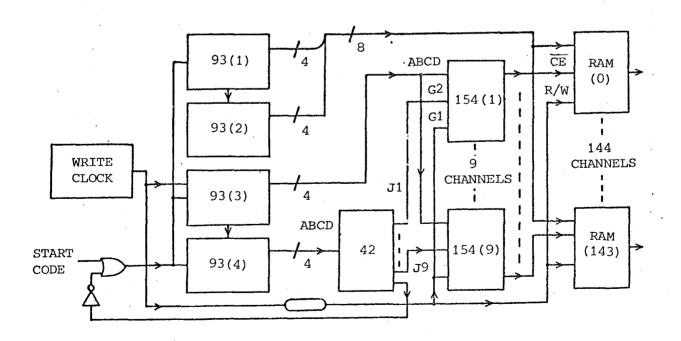


Fig. 4 Sequential write mode 1.

## Sequential write mode 2 (Fig. 5)

Again three code generators are used in this mode, but in a different combination from the write mode 1.

The 1st code generator consists of 93(1) and 93(2). This is driven directly by the write clock, and generates 256 different 8-bit codes (one code per clock pulse). This output is fed into the address bus of the RAMs so that one address of each RAM is selected at a time. Only one address throughout the RAM can be selected, when the CE terminal of a particular RAM is activated.

The 2nd code generator consists of 93(3). This is driven by the 256th code of the 1st code generator, and generates 16 different 4-bit codes (one code per 256 clock pulses). This output is fed into channel selectors 154(1) to 154(9) so that one of 16 channels in each 154 is selected at a time. Only one channel throughout all the 154s can be selected, when the CE terminal of a particular 154 is activated.

The 3rd code convertor consists of 93(4). This is driven by the 16th code output of 93(3), and generates 9 different 4-bit codes (one code per 4096 clock pulses). This output is fed into 154(1) to 154(9) so that one of the 154s is selected at a time. The combined effect of 1st, 2nd and 3rd code generators selects only one address throughout all the RAMs at a time, and this address is activated by a clock pulse through the delay circuit and the R/W terminal.

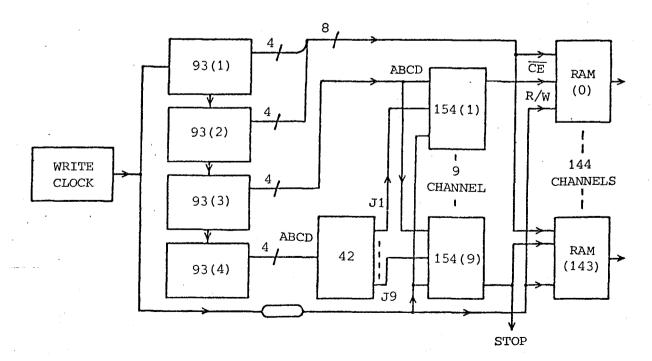


Fig. 5 Sequential write mode 2.

## Sequential read modes 0 and 1 (Fig. 6)

Once data is written, by either sequential write mode 1 or 2, there is no difference in the order of written data in the memory. Therefore, any sequential read mode can be applied to read the memory written by either sequential write mode 1 or 2.

For sequential read mode 0, one code generator, consisting of 93(1) and 93(2), is used. This is driven by the read clock, through a gate which can be ignored in this mode, and generates 256 different 8-bit codes (one code per clock pulse). The output of the code generator is fed into the data bus to which all the RAMs are connected so that they are read simultaneously, data written in each set of RAM (256 words) being read sequentially. The reading data is cycled without a break until it is stopped externally.

For sequential read mode 1, two code generators are used. The first code generator consists of 93(1) and 93(2). This works in the same way as that in sequential read mode 0, except the gate is activated in this mode. The second code generator consists of 93(3), 93(4) and 93(5). This is driven directly by the write clock, and generates one-bit code (or an on-or-off code), its on-period and off-period being equal to the period of 256 clock pulses. This output is fed into the above-mentioned gate, so that the reading data is cycled at intervals until the cycling is stopped externally.

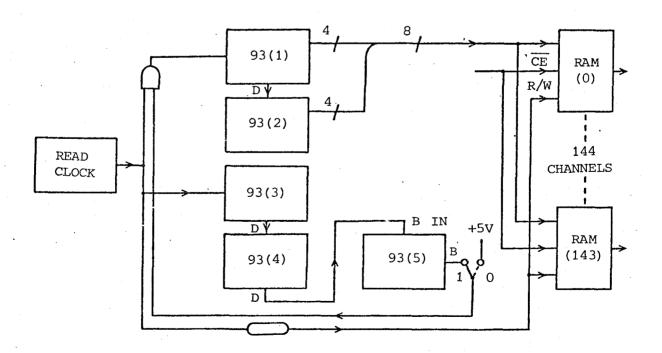


Fig. 6 Sequential read modes 0 and 1.

## Random write/read mode (Fig. 7)

An input for the random read mode of this system must have the format shown in Fig. 7 at the input terminal of the system. This particular format is used for other parts within the model, and simplifies its hardware. If arbitrary input is given, this must be converted into the specified format before it is fed into the memory system.

Three registers with a timing circuit are used for converting this bit-parallel word-serial form into bit-parallel word-parallel form.

The 1st register, consisting of 75(1) and 75(2), is used for holding address A1 (8-bit word). This output is fed into the addresses of all the RAMs through the data bus. Only one address throughout all the RAMs can be selected at a time, if a particular RAM is activated through its CE terminal.

The 2nd register, consisting of 75(3) and 75(4), is used for holding address A2 (another 8-bit word). The output of this register is divided into two parts: 4 least-significant bits and 4 most-significant bits. The 1st part is fed into selector 154(1) to 154(9) in parallel so that a particular terminal within each 154 is selected. Only one particular terminal throughout all the 154s can be selected at a time, when a particular 154 is activated through its CE terminal. The 2nd part of the register output is fed into another selector, 42, so that one of its 9 channels, which are connected to 154(1) to 154(9), is selected. The combined effect of the 1st and 2nd registers selects only one address throughout all the RAMs at a time.

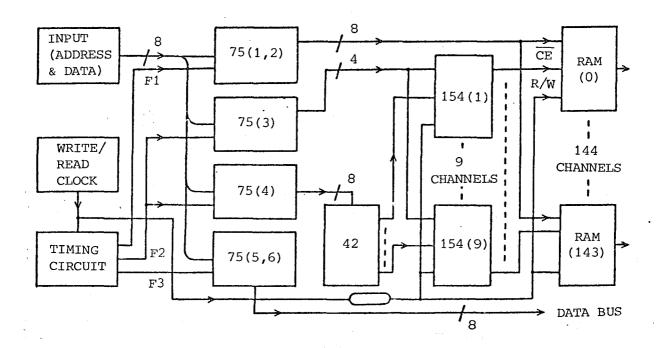


Fig. 7 Random write/read mode.

The 3rd register, consisting of 75(5) and 75(6), is used for holding data D (8-bit word). This output is fed into all the RAMs through the data bus. Since only one address throughout all the RAMs is already selected, the data is written into this address by activating this address through its CE terminal.

The operation of the random read mode is carried out in a similar way to its write mode. A set of address codes, A1 and A2, from which the data should be read, is fed into the system through its input terminal so that a particular address is selected. The written data in this address is read through the data bus by activating the RAMs.

Section (n-1)		Sect	ion n	Section (n+1)	
<u></u>	Add:	ress	Data	Space	)
\$	A1	A2	D	-	}

Fig. 8 Format of input for the random write/read mode.

One section corresponds to 4 clock pulses,
each sub-section corresponds to one clock pulse.
Each sub-section consists of a parallel 8-bit code.

## '2.4 Choice of a memory type

The following conditions are required for the type of RAMs in this application:-

- 1. The whole memory can be divided into sections of (8-bit X n m addresses) each of which can be controlled separately, where n > 140 and m > 200;
- 2. The leakage currents of all the input terminals of the memories should be small;
- 3. The number of control terminals per section should be small;
- 4. The number of different power supply voltages and the total power dissipation should be small; and
- 5. The total cost should be small.

Requirement  $\underline{2}$  is due to a large number of terminals connected to a single data bus which is driven by a small number of output circuits. Requirements  $\underline{3}$  and  $\underline{4}$  are due to the use of a large number of components. Requirement  $\underline{5}$  is obviously due to a limited budget.

AM9112 (AM Device), Intel 2112A, Signetics 2112 and TMS4043 (Texas Instruments) can meet the range of requirements. They are essentially the same type as a 256-word by 4-bit random access memory element using N-channel MOS devices integrated on a monolithic array. It has only two control terminals, other than address and data terminals, and is operated by a single +5V power supply requiring 150 mW. The input leakage currents of these devices, however, differ between manufacturers, AM9112 and Intel 2112A being considerably less than others. Taking into account the availability in this country at the time of designing, therefore, AM9112 has been chosen. At the time of purchase, the price of this device was £1.50 each (+300 quantity).

# 2.5 Choice of a type of DAC and output circuit

The analogue output of the input memory is required to drive up to 6 LEDs (forward current approximately mA each) in series with the maximum current of 12 mA (8 mA dc bias +4 mA pk-pk signal). The physical size of a DAC in this application should be small due to the limited space on the circuit board. The cost of each DAC should be small, because this is the most expensive single component in the system and 144 units of them have to be used. For these reasons, only monolithic type 8-bit DACs were considered. For example,

AD7523	(AD Device)	£1.71	(100+	price)
MC1408L	(Motorola)	2.17		3
DAC-08CQ	(PMI)	2.26		`
NE5007N	(Signetics)	2.40		
ZN425E	(Ferranti)	3.50		

Since the output current required exceeds the maximum current of any of these DACs, it is necessary to add a current amplifier, and to use power supply voltages other than +5V. The combination of NE5007N and 741 (an OP amplifier) has been chosen, taking into account the best availability. Note AD7523 requires an external component which makes the highest total cost in these examples.

NE5007N has negative and positive output-current terminals which can be chosen for the purpose. The polarity of the bias current can also be chosen, when it is added to the signal current through the input of the 741. These make four different combinations as shown in Fig. 9. By considering the format of the programme (described in a separate paper), the circuit shown in the 2nd column of Fig. 9 has been chosen.

	RESPONSE TO A POSITIVE-GOING STEP INPUT (DIGITAL)	CURRENT OUTPUT /	OPTICAL OUTPUT	VOLTAGE OUTPUT IN A GRIP
1	→DAC DAC		:	·——
2	-E <sub>B</sub> →DAC <sup>2</sup> 1	[s_B]	•——	•
3	+E <sub>B</sub> DAC			·
4	DAC DAC	[sB]		•——

Fig. 9 Possible combinations of the output-circuit configurations.

B: Bias S: Signal

#### 3. CIRCUIT DESCRIPTION

Fig. 10 shows the circuit diagram of the input memory, except its power supply. This circuit includes the five circuits shown in Figs. 4, 5, 6 and 7, and other peripheral circuits. The peripheral circuits are as follows:-

#### Switches

The five different modes of operation are obtained by using several manual and automatic switches which are controlled by the former. The manual switches are:-

Sequential-or-random switch, Write mode switch (1 or 2), Read-period selection switch (1, 2 or 3), and Start switch.

The first switch is on the rear panel, and the rest of the switches are on the front panel.

The automatic switches consist of 20 sets of 1-pole 2-way logic switches, contained in five IC packages,  $\underline{157(1)}$  to  $\underline{157(5)}$ , and eight sets of on-off switches contained in  $\underline{4016(1)}$  and  $\underline{4016(2)}$ . The first 16 sets are used for switching between sequential and random modes. The last 4 sets of 2-way switches and all the on-off switches are used for switching between write and read modes.

#### Clock

The clock consists of a crystal (10 MHz  $\pm$  10 ppm) and two units of 04(3) (in a linear operation with two 1K feed-back resistors). The frequency is reduced by 90(1) to 90(4) and 93(4) and 93(6) to nf, nf/2 and nf/3, where n can be chosen (by an internal semi-fixed switch) to be 1 MHz, 100 kHz or 10 kHz. The final choice of the frequency is carried out by the read-period selector switch.

#### Tape-control circuit

This circuit consists of  $\underline{121(3)}$ , 2/3 of  $\underline{00}$ ,  $\underline{30}$ , 1/2 of  $\underline{04(2)}$ ,  $\underline{121(2)}$  and 1/2 of  $\underline{93(5)}$ . The timing diagram for this circuit is shown in Table 10.

When switch START is activated manually, 121(3) generates a pulse. This sets the FF, consisting of 00, to a state which starts an external tape-reader. 121(3) also generates another pulse at the same time, and this pulse sets the output of 93(5) low. The start code (1111 1111) on the tape is then decoded by 30, and enters into 93(5) through 121(1). This sets the output of 93(5) high. When the tape-reading has been completed, the end code (again 1111 1111) on the tape is detected by 30. This enters into 93(5) and sets its output low. At the same time, 121(2)/6 generates a reset signal, RST, and this enters into 00/13 just before the output of 93(5) is lowered. The signal from the 00/11 resets the FF so that the tape-reader is stopped. When the whole system is switched on for the first time, a pulse is generated at 04(2)/10, and this resets the whole control circuit.

## Write/Read signal generator

Several parts of the memory control circuit require a set of voltages by which the write or read mode of the whole system is indicated. This signal is generated by 93(5) (low in a write mode and high in a read mode), and is shown as CSW in Fig. 10. The complementary signal to this signal is also generated by 04(1)/8,9, and is shown as CSW in Fig. 10. The state of CSW is indicated by a red LED on the front panel; e.g. an ON state of this LED indicates that the whole system is in a read mode.

## R/W-terminal control signal

Each RAM requires a signal to control its R/W terminal. This signal should be high in a read mode, and low for about 100 ns after every one words has entered into the memory. Such a signal is generated by passing the write clock through a pulse delay circuit, 04(1)/1,2,3,4. This signal is shown as R/W in Fig. 10.

## CE-terminal control signal

Each RAM also requires a signal to control its CE terminal. This signal should be high normally, and should be low only after each address code has entered into a RAM until just before it is removed. The actual low period of the signal differs between the write and read mode, because the period of the write and read clock are different. Such a signal is obtained at the input terminal of each 08 in circuit board M5, M12 and M19 (140 terminals in all).

This signal is generated by the write or read clock separately, and the signal is passed through a pulse-width control circuit, 121(1), and a pulse-delay circuit, 04(1)/1,2,3,4. After this, the signal passes through different circuits, depending on the write or read mode. In a write mode, the signal passes through 32/4,6; and a selected channel of 154(1) to 154(9); and enters into the input terminal of a selected 08 on boards M5, M12 and M19. In a read mode, the signal passes through 32/1,3; one of 04(1)/5,6, 04(1)/11,10 or 04(1)/13,12; also all the 04s on board 040, 041 or 041 and 042 or 043. After 044 input terminal of all the 045 on boards 045, 046 or 049. After 049, the circuit is divided into three groups, because of their 'fan-out' capability.

## Read-pulse width control circuit

When a set of words written in a RAM is read continuously, there are inherent intervals between the adjacent words. When such a set of words is converted into an analogue voltage (or current) by an ADC, its output also contains the intervals other than the converted values of useful signal. In order to overcome this, each interval must be adjusted to be very small compared with the period of each useful signal voltage. This adjustment is carried out by a potentiometer (100K) connected to 121(1)/9.

## Register-timing circuit

Three groups of registers, 75(1) to 75(6), shown in Fig. 7, require three pulses, F1, F2 and F3, which have different widths and timings. These pulses are generated by 93(7), 2/4 of 04(2), and 3/4 of 08. When all the registers have completed the registration of address and data, another pulse is required to execute a write or read of the data into the address. This pulse is taken from 08/3, and passed through another pulse-delay circuit, 04(2)/1,2 and 04(2)/3,4, a pulse shaper, 121(4), and fed into the same circuits as for a sequential mode.

## Memory, DAC and output circuit

The system has 140 channels of analogue current output each of which drives up to 6 LEDs (824 in all). All the channels are identical, and one of them is shown on the right hand side of Fig. 8. One channel consists of two RAM packages, 9112(1) and 9112(2), two IC packages of switching circuit, 4066(1) and 4066(2), a DAC, 5007, and a current output circuit, 741.

The address terminals of the RAMs are permanently connected to the address bus (8 channels). The data terminals (input and output common, also 8 channels) of the RAMs are permanently connected to the input terminals (8 channels) of the DACs. The data terminals of the RAMs are also connected to the data bus through the switching circuits only when the system is in a sequential write mode, or in a random write and read modes. This arrangement is necessary for a simultaneous reading of RAMs, in a sequential mode, each of which store different data.

The reference voltage (terminal 15) of each DAC is taken from the  $\pm 12V$  supply line through a 50K potentiometer by which the full scale of the output is set.

The output current (at terminal 4) of the DAC is proportional to its digital input, the maximum current being mA. The final current output required to drive up to 6 LEDs in series is

### 8 mA (bias current) + 4 mA pk-pk (signal)

The bias current is necessary to operate each LED in a linear range. In order to satisfy these conditions, a 741 is inserted between each DAC and a set of LEDs. The output signal current of the DAC is converted once into a signal voltage by a 1K resistor. Then a constant voltage of -12V is added to the signal voltage through a 30K resistor, which is connected to the inverted input terminal of the 741. The output current of the 741 is sampled by a  $100\Omega$  resistor as a voltage, and this is fed back to the inverted input of the 741. In this way, the output current becomes independent of the load (from a short circuit to 6 LEDs). The details of the design of this part of the circuit are described in Appendix .

The DACs and output circuits are operated by a ±12V power supply for driving up to 6 LEDs, while the rest of the system is operated by a single +5V power supply.

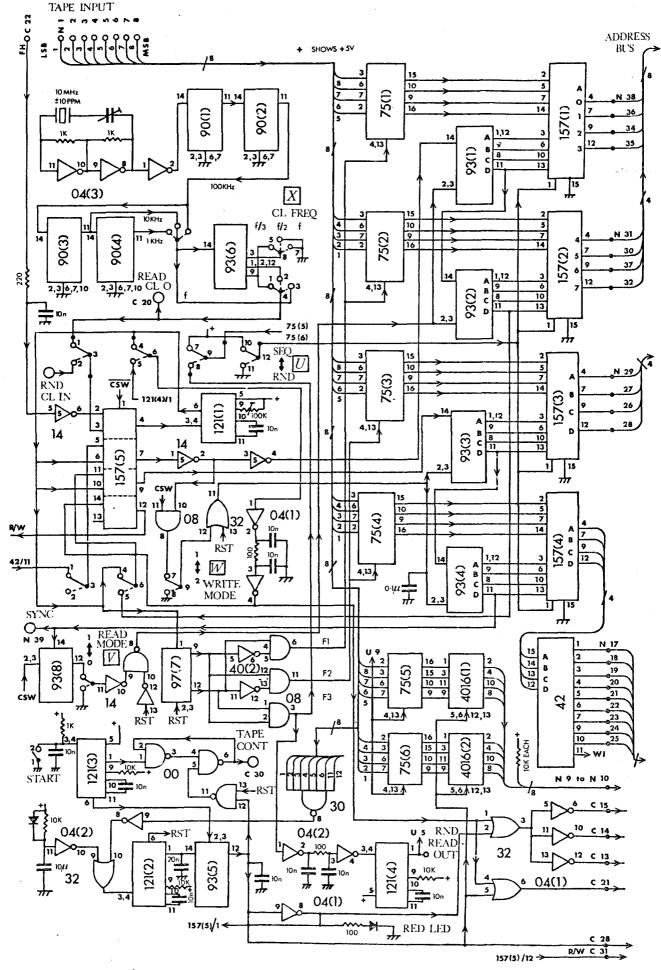


Fig. 10 Circuit diagram of the input memory. (Continued to the next page).

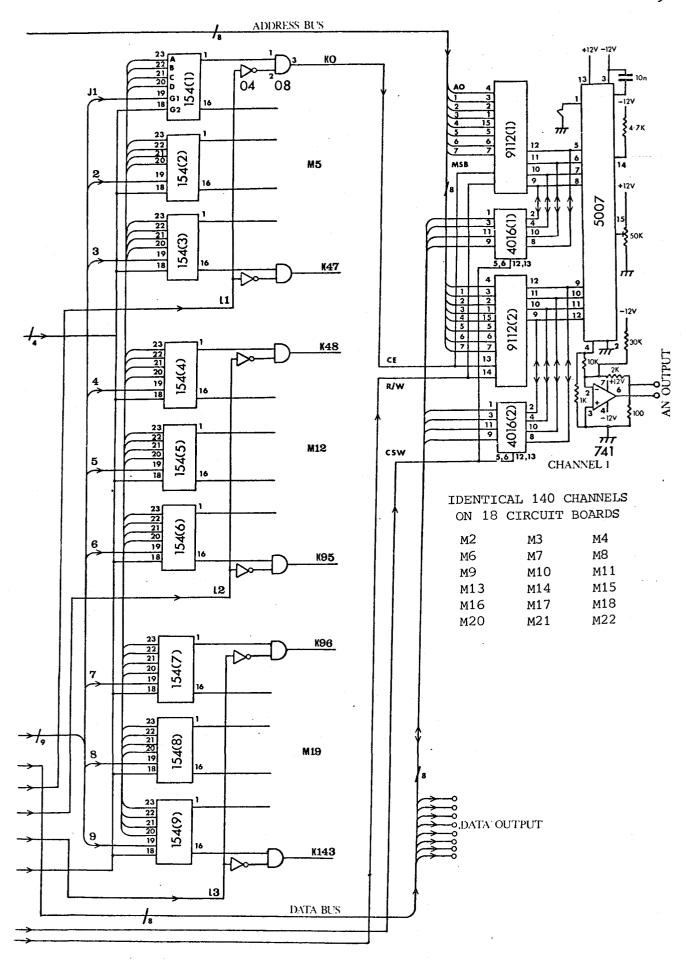


Fig. 10 (Continued from the previous page).

#### Read modes control circuit

This circuit selects read mode 0 or 1, the former being a repeated reading of the memory without intervals, and the latter with intervals of 256 words. The circuit consists of 93(8), 14/10,11 and 08/8,9. 93(3) and 93(4) are also used as a pulse counter in the reading modes.

The read clock enters in parallel into the address-code generator, 93(1) and 93(2); and the pulse counter, 93(3) and 93(4). The reset signal, which is generated only at the start of reading, enters into the two circuits simultaneously, so that they work in complete synchronization. Note the reset signal, RST, enters into the 93(1) and 93(2) through 14/13; and into the 93(3) and 93(4) through  $32/\overline{12}$ .

In read mode 0, 93(3) and 93(4) have no effect on reading, although they are working and pulses (pulse width 256 words, intervals also 256 words) are obtained at 93(8)/12. Note switch 'V' cuts off the output of 93(8)/12. Consequently, the reading of the memory continues without intervals.

In read mode 2, where switch 'V' connects  $\underline{93(8)/12}$  to  $\underline{14/11}$ , the pulses enters into the  $\underline{93(1)/2}$ , 3 and  $\underline{93(2)/2}$ , 3 so that they are interrupted periodically (both the active and rest periods of 256 words). See Table 12 for the timing diagram.

### Protection circuits

The data bus is linked with other circuits by  $\underline{4016}$ s (8 channels in the control circuit board, and 560 channels in the memory boards). In a sequential read mode, all the  $\underline{4016}$ s are in an off state, and each channel of the data bus is electrically floating with a very high resistance. In order to avoid the electro-static charge of this line, each line is connected to +5V line through a 10K resistor as shown near 4016(1).

#### Noise filtering circuits

The power supply terminals of each of 93s and 121s are shunted by  $0.1\mu$  capacitor within each package.

Other than the above usual method of noise filtering, the following two circuits are important in this particular control board:- A 0.1 $\mu$  capacitor by-passing the terminals 93(3)/2,3 and 93(4)2,3 to earth: without this capacitor, the address code in write modes will be disturbed, resulting in a periodical noise in the final output waveform.

A 0.1 $\mu$  capacitor with 200 $\Omega$  resistor by-passing the input from C22 to earth: without this filter, a similar effect to the above will appear.

#### 4. POWER SUPPLY AND PROTECTION CIRCUITS

In order to drive the input memory, three regulated dc-voltages are required as shown in Table 2. Three different types of power supply units (all standard products) are employed as shown in Table 3. The memory cabinet and power supply cabinet are separate, connected only by a cable (about 30 cm long) with a 20-pin connector. Beyond the connector, an independent conductor is used for each circuit board. Each voltage is monitored at the connector, and fed back to the voltage sensing terminals of each power supply, except for the +12V unit which does not have sensing terminals.

The main memory units withstand between -0.5V and +7.0V, while the DAC units withstand between -18V and +18V. Therefore, protection against an accidental supply-line voltage rise is required. The accident which is most likely to occur is that the -12V or +12V line makes contact with the +5V line within the system. Another accident, which is less likely to occur, is the 240V ac-line contacting any of the dc lines.

In order to minimize the risk of such an accident, most of the -12V or +12V line terminals are surrounded by conductors which are connected to the ground line.

As a further protection, the circuit shown in Fig. 12a has been added to the power supply. This circuit works as follows:-

### Accidental contact of the +12V line to the +5V line

The voltage on the +5V terminal is constantly monitored through the voltage sensor of the circuit (shown in Fig. 12a), and this is compared to the reference voltage of 6.2V (fixed by a zener diode). If the sensor voltage becomes higher than the reference voltage, comparator 319(1) generates a positive-going voltage which activates thyristor 10655(1). Then the +12V line is shunted by the thyristor, within 80 nano seconds. At the same time, comparator 319(2) also generates a positive-going voltage and activates thyristor 1065(2). This thyristor activates a latch relay by which the 240V ac-line for the whole system is cut off within about 50 milli seconds.

Since 319(2) and 106S(2) have to be operated after the regulated +12V power output is shut down, they are driven by an unregulated voltage (+17V to +20V) which is available within the same power supply unit even after the shut down.

The latch relay has been designed for the purpose, by using a standard micro switch and a solenoid. Fig. 13 shows its construction, and Fig. 14 shows its operation. Once the relay is activated by the primary voltage, the secondary circuit is opened, and stays in an open state independent of the primary voltage after the first activation. The relay can be reset only by manual operation, after the cause of the accident has been rectified.

### Accidental contact of the -12V line to the +5V line

The +5V line is kept in a regulated condition, even when the -12V line contacts it, except for an instantaneous voltage drop (not below 0V). During an accidental contact, about 150 mA of current flows into the -12V supply terminal.

The protection circuits have been tested successfully with the actual full load.

Table 2 DC power requirement

Circuit board	Number of	Typical current per board			Unit
CIICUIC DOALG	boards	+5 <b>v</b>	-12V	+12V	Onic
м1	1	480	. –	_	mA
M5, M12, M19	3	350	-	-	mA
M2 to M22 except the above 4 boards	18	500	72	155	mA
Total current		10530 ·	1296	2790	mA
Total power		52.7	15.5	33.5	W

The power requirement for the +12V line depends on its load; the value shown is the maximum. The total power of the three voltages is 101.5 W.

Table 3 Power supply units used

Nominal voltage		+5	-12	+12	v
Maximum current		20	2	3	A
Make		Gould	Gresham	Countant	_
Model		MG5-20	GXL-12/2	нс12-3.0	· _
Regulation :	method	Switching	Linear	Linear	_
	Voltage	115 to 240	100 to 250	105 to 240	V
Input	Frequency	45 to 440	45 to 450	50 to 60	Hz
	Line regul. ±10% change	±0.1	±0.01	±0.05	ફ
	Load regul. Zero to full	±0.1	±0.04	±0.1	96
Output	Temp. coeff.	±0.01	±0.02	±0.03	%/ <sup>°</sup> C
	Impedance @ 100 kHz	100	250	250	mΩ
	Noise @ bandwidth	50 30	2.0	3.0 20	mV pp MHz
	Over voltage	120 to 130	No	No	% FS
Protection	Over load	110	110	110 to 250	% FS
Operating temperature		-10 to +70	-15 to +50	0 to +50	°с
Power efficiency		70	50	55	8
Case dimensions		164×105×88	204×108×87	143×114×63	mm³
Weight		2.0	2.3	1.8	Kgr

All the figures are based on manufacturers' specifications.

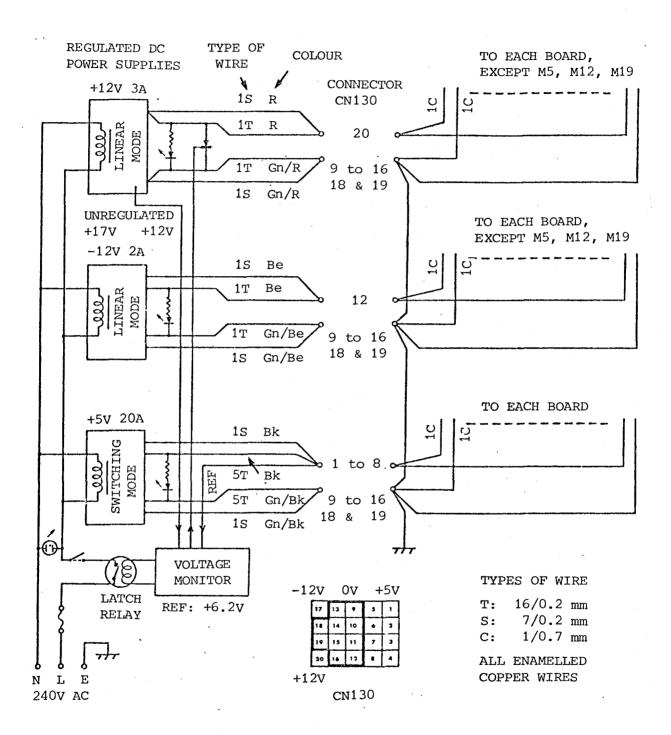


Fig. 11 Circuit diagram of the power supply unit.

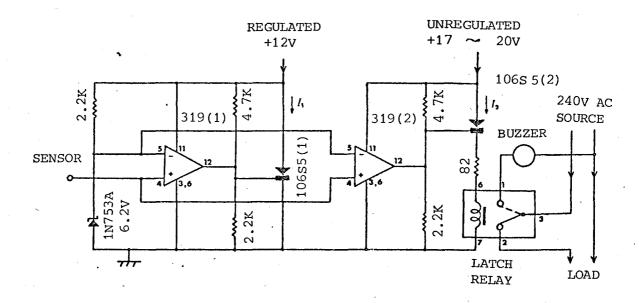


Fig. 12a Voltage monitor and protection circuit.  $I_1 = 1.8 \text{A after } 10655(1) \text{ has been activated by the instantaneous rise (>6.2V) of the sensor voltage.}$   $I_1 = 10 \text{A, if the sensor voltage is kept >6.2V.}$   $I_2 = 75 \text{mA after } 106S(2) \text{ has been activated by the same sensor, either instantaneously or continuously.}$ 

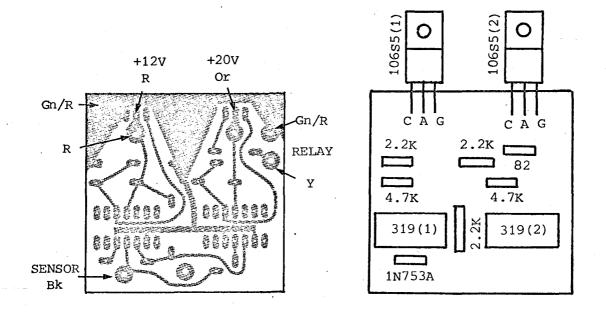


Fig. 12b Component arrangement of the board shown in Fig. 12a.

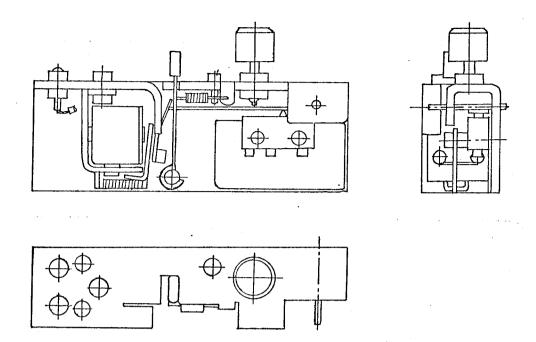
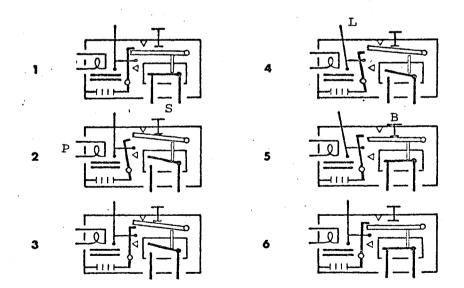


Fig. 13 Construction of the latch relay (full scale). actual unit is contained in a transparent case with an 8-pin connector.



Action of the latch relay shown in Fig. 13. Fig. 14

- Normally the secondary circuit, S, is closed.

  If the primary circuit, P, is energized, S is

  For resetting, press the lever, L.

  Press the button, B, and

  Release L. If the primary circuit, P, is energized, S is opened.

#### 5. PHYSICAL CONSTRUCTION

The previous input memory was linked with external systems through mode then 300 terminals which are connected internally to 22 printed-circuit board connectors. These parts, including a board frame and outer cabinet, have been reused for the new input memory in order to save work. In other words, the physical dimensions and terminal arrangements of all the new circuit boards have been designed to be the same as the previous ones, except for the control circuit board, M1. This has made the component density on each new board very high, and even the use of multiple flat cable on a board was necessary. This has also made the order of actual channels on each circuit board appear odd.

The input memory system has been divided physically into two parts: a main memory cabinet and a power supply cabinet, as shown in Fig. 15.

### Memory cabinet

This consists of:-

Control circuit board, M1, with a front control panel;

Output monitor terminals;

3 sub control-circuit boards, M5, M12 and M19;

18 memory circuit boards, M2 to M4, M6 to M11, M13 to M18, M20 to M22;

Rear panel with a switch and connectors;

6 sets of multiple connector for output;

Board frame with connectors and wirings; and

Cabinet case with its front and rear covers.

Fig. 16 shows the three types of circuit board, 22 boards in all. Figs. 17 to 23, and Tables 4 to 6 show their details. Tables 5 to 8 show connections of terminals in the memory cabinet.

Circuit board M1, which requires more frequent and complex examinations than other boards, has long flexible wires between its edge-connections and the cabinet, so that the board can be examined in a working state outside the cabinet.

The rest of the boards have to be disconnected from their edge connectors for detailed examinations. Note, the 18 memory boards (M2 to M22) can be examined with the memory test unit (chapter 6.1). The three boards (M5, M12 and M19) have enough spaces for examination in a working state, when the memory boards are extracted from the cabinet.

A method of extracting the memory boards with a simple tool is shown in Appendix 5.

## Power supply cabinet

This cabinet contains the three power-supply units, voltage monitoring circuit, and protection circuits with its reset switches.



Fig. 15 Memory cabinet (top) and power supply cabinet (bottom).

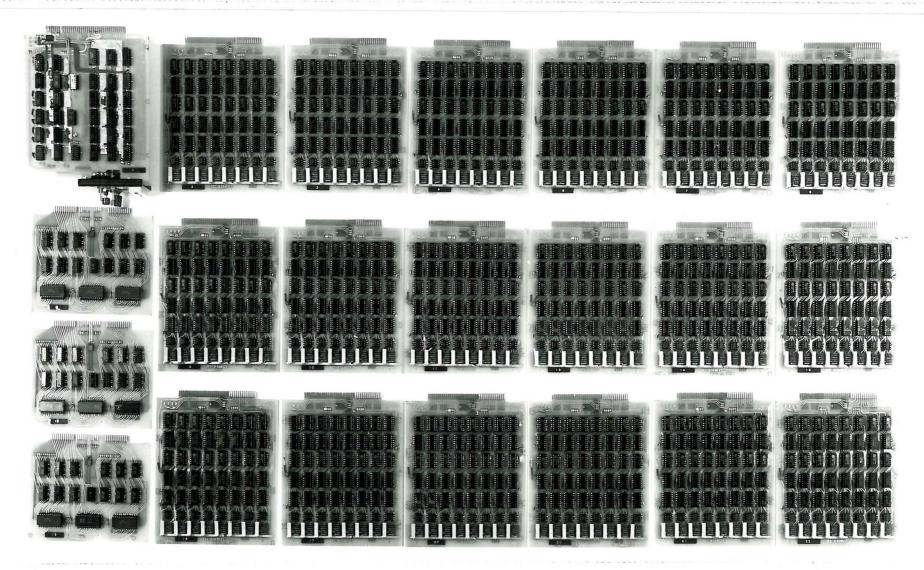


Fig. 16 The circuit boards contained in the memory cabinet.

Control circuit board, M1 (top left); three sub-control boards,

M5, M12, M19 (bottom left); and 18 memory boards, M2 to M22.

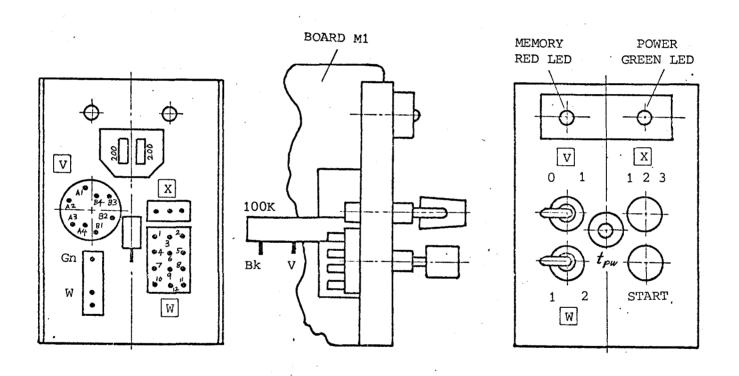
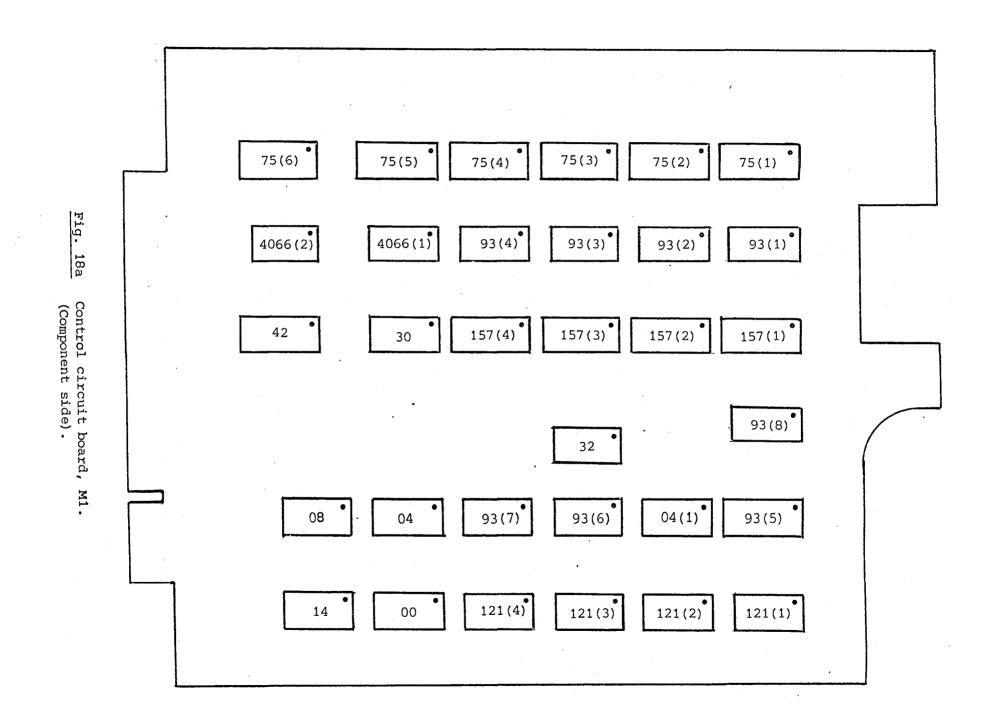


Fig. 17 Front panel of the memory cabinet.



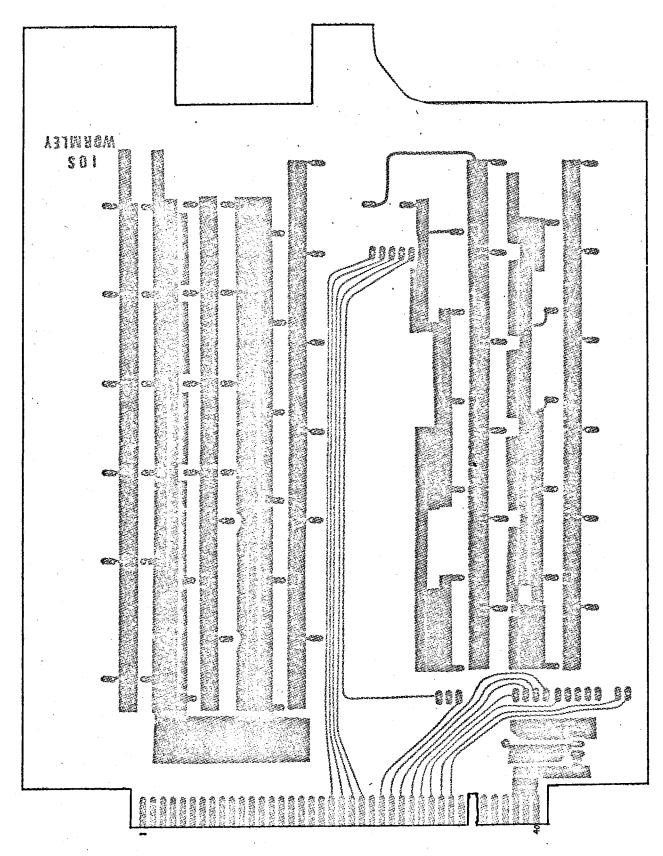


Fig. 18b Control circuit board, M1. (Conductors on the component side).

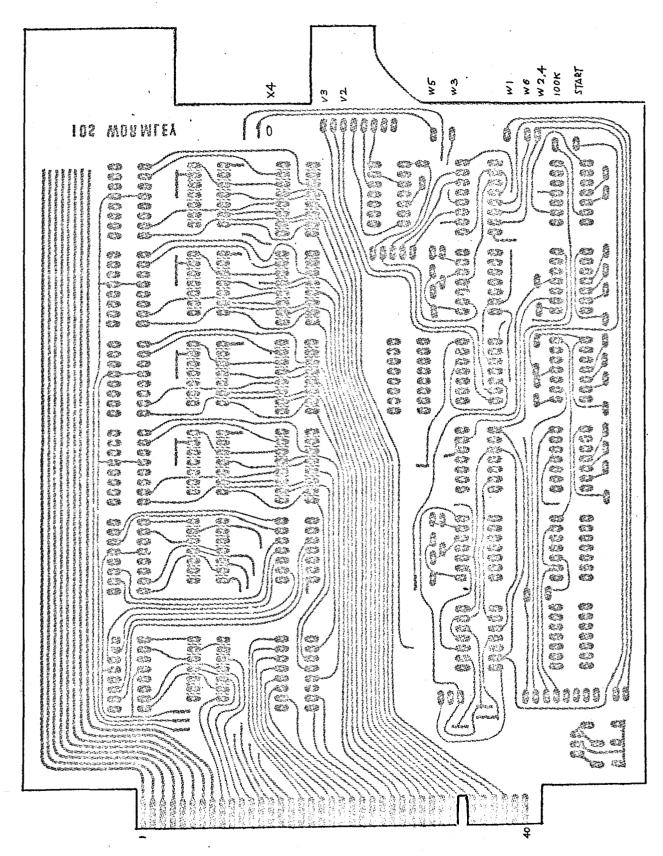
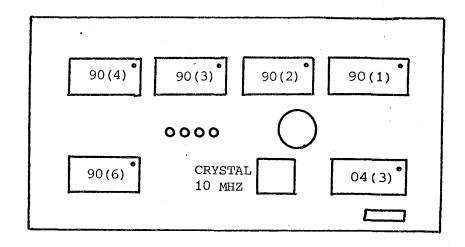


Fig. 18c Control circuit board, M1.

(X-ray view of the non-component side).



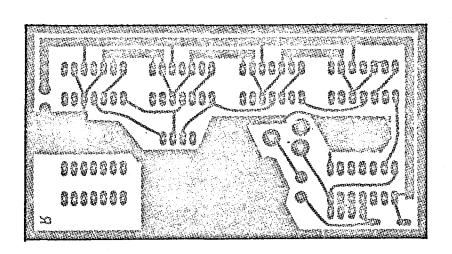


Fig. 18d Additional board to the control circuit board, M1.

Component side (top), and the X-ray view of the non-component side (bottom).

Table 4 Connections of the control circuit board, M1.

Board Ml		Connected		I	Board		Connected
pin No.		to			pin l	No.	to
N 1 N 2 N 3 N 4 N 5 N 6 N 7 N 8	Bn R Or Y Gn Be V Gy	CN103/1 /2 /3 /4 /5 /6 /7 /8	Tape Out 1 2 3 4 5 6 7 8				
N 9 N10 N11 N12 N13 N14 N15 N16	Bn R Or Y Gn Be V	CN103/14 /15 /16 /17 /18 /19 /20 /21	Data Bus 1 2 3 4 5 6 7 8		C13 C14 C15 C16	Or/Gn Or/Bn Or/R Bn	M19/N27 L3 M12/N27 L2 M5/N27 L1 M1/U1 (RP)
N17 N18 N19 N20 N21 N22 N23 N24 N25	Bn R Or Y Gn Be V Gy W	M 5 /23 /24 /25 M12 /23 /24 /25 M19 /23 /24 /25	J1 J2 J3 Select. J4 J5 J6 J7 J8 J9		C17 C18 C19 C20 C21 C22 C23 C24 C25	W Gy Or/Bk Gy/Be W Or Be	M1/U12 (RP) M1/U9 (RP) SEQ R CLK O (RP) M5,M12,M19/22 'P' CN103/9 W-CL M1/U3 (RP) M1/U6 (RP) M1/U8 (RP)
N26 N27 N28 N29	Bk .Gy W	M5 /18 M12 /17 M19 /19 /16	Select. B D		C26 C27 C28 C29	Y/R W/Bk R/Bk Y	RID R CLK O (RP) Not used C9 of all 18 bds M1/U4 (RP)
N30 N31 N32	V Be Gy	/7 /6 /8	A4 Address A7		030 <b>0</b> 31	W/Or W/Gn	CN103/10, 12 Cll of all 16 bds
N33		Slot	Date:	[	C33		Slot
N34	Or	18bds/3	AZ	<b> </b>  .	C34	Gn/Bk	Common (OV)
N35	R	/4 /2	A3° A1		C35 C36	•	
N36 N37	l I Bn	/5	A6		C37	·	
N38	Gn	/1	AO	1 1	C38		
N39 N40	Or/	<u> </u>	SYNC O (RP)		C39 C40	Bk	+5V supply

(RP): Rear panel R-CL: Read clock

18bds: 18 boards M2 to M4, M6 to M11, M13 to M18, M20 to M22.

C : Component side

N : Non-component side

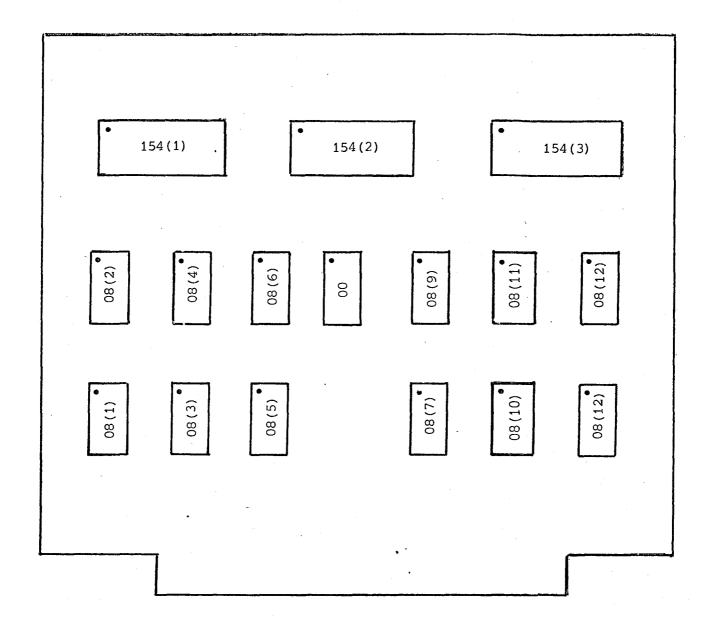


Fig. 19a Sub-control circuit board, M5, M12 or M19. (Component side).

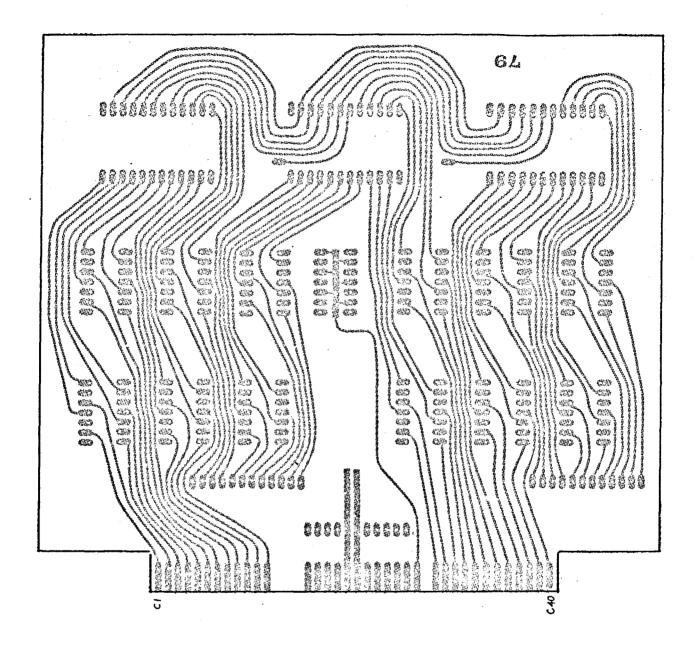


Fig. 19b Sub-control circuit board, M5, M12 or M19. (Conductors on the component side).

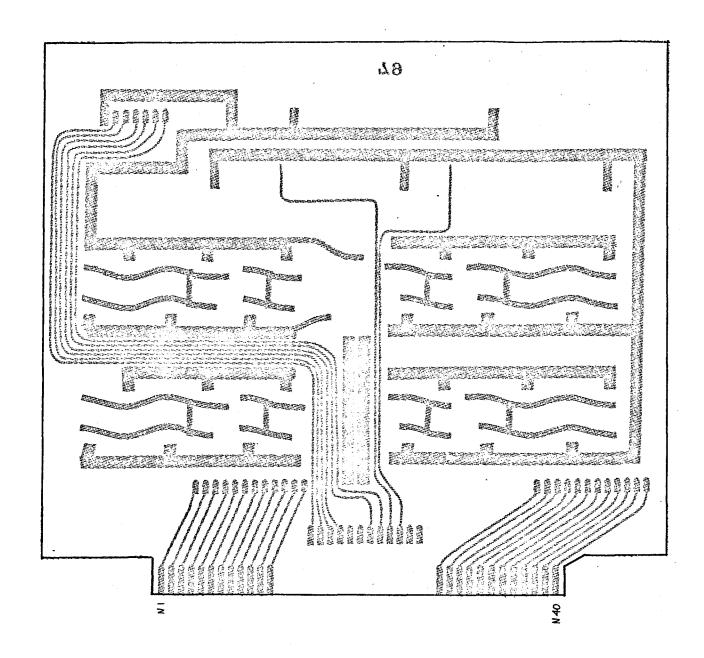


Fig. 19c Sub-control circuit board, M5, M12 or M19. (Non-component side).

Table 5 Connections of boards, M5, M12 and M19.

130	Cannasti		1	M12	Connecti	o 20	)	M1.9	Commonti	
M5	Connecti		-		Connection				Connection	V 06
Cl	M2/C10	КО		01	м9/с10	K48		Cl	M16/C10	K 96
C 2	C11 (	K l		C 2	C11	K49	į	C 2	C11	K 97
03	C12	K 2		C 3	012	K50		C 3	C12	K 98
C 4	C13	ĸ 3		C 4	C13	K51		C 4	C13	K 99
	013								1177/070	
05	M3/C10	K 4		C 5	и10/с10	K52	1	C 5	M17/C10	K100
C 6	C11	K 5		C 6	C11	K53		C 6	C11	K101
C 7	C12	K 6		C 7	C12	K54	l	C 7	C12	K102
				C 8	C13	K55		c 8	C13	K103
	013									
09	M4/Cl0	к 8		C 9	M11/C10	K56		C 9	M18/C10	K104
C10	Cll	K 9	· ·	C10	C11	K57		C10	C11	K105
cli	C12	KlO	i	Cll	C12	ĸ58	ł	C11	C12	K106
C12	C13	Kll	,	C12	C13	K59	1	C12	C13	K107
					7/2 /7/00			C13		A
C16	M1/N29	A		C16	M1/N29	A			M1/N29	
C17	N27	В		C17	N27	В	l	C17	N27	В
C18	N26	C ·		C18	N26	C	l	c18	N26	C
	N28	D		C1.9	N28	D	l	019	NIS	D
019										
C50	CN130/1	+57		C20	ON130/1	+5₹	]	C20	CN130/1	+5V
021	9	OV		C21	9	VO	ĺ	C21	9	OV
C22	M1/C21	P		C22	M1/C21	P	†	C22	M1/CSJ	P
				C23	N20	J4	Ì	C23	N23	J7
023	N7	Jl								
C24	NIS	J2		C24	N21	J5		C24	N24	J8
C25	N19	J3		C25	N22	J6		C25	N25	J9
026	-			C26	_			C26	_	-
				C27	M1/C14	1.2		C27	M1/C13	13
C27	M1/C15	Ll					l			
C29	M2/C27	K24		029	M9/C27	K72	İ	029	M16/027	K120
<b>c</b> 30	<b>C</b> 28	K25		030	<b>c</b> 28	K73	İ	C30	<b>C</b> 28	K121
C31	<b>C</b> 29	K26		031	029	K74		031	<b>C</b> 29	K122
				C32	<b>c</b> 30	K75	l	C32	<b>c</b> 3ó	K123
032	<b>c</b> 30	K27					1			
C334	M3/C27	K28		C33	M10/C27	K76		c33	n17/027	
C34	C28	K29		C34	<b>c</b> 28	K77	ļ	C34	<b>C28</b>	K125
¢35	<b>C</b> 29	K30		<b>c</b> 35	<b>C</b> 29	K78	i	<b>C35</b>	<b>C</b> 29	K126
					<b>C</b> 30	K79		C36	<b>c</b> 3ó	K127
<b>C</b> 36	<b>c</b> 30	K31		C36			1			
C37	M4/C27	K32		C27	M11/C27	K80		037	M18/C27	K128
<b>c</b> 38	C28	K33		C38	C28	K8I	1	C38	C28	K129
<b>c</b> 39	<b>C</b> 29	K34		<b>c</b> 39	<b>c</b> 29	<b>K</b> 82		039	029	K130
1 232					<b>c</b> 30	K83	ł	C40	<b>C3</b> 0	K131
C40	<b>C30</b>	K35		C40			ĺ			
N 1	M6/C10	K12		Nl	M13/C10	K60		Nl	M20/C10	Klos
N 2	Cll	K13		N 2	Cll	K61	1	N S	C11	K109
N 3	C12	K14		N 3.	C12	K62		N 3	· C12	K110
						K63		N 4	C13	Klll
N 4	C13	K15		N 4	C13					
N 5	M7/C10	Kl6		N 5	M14/C10	K64	ł	N 5	M21/C10	K112
N 6	C11	K17		N 6	C11	K65		N 6	C11	K113
N 7	C12	Klö		N 7	C12	K66	l '	N 7	C12	K114
					C13	K67	l	N 8	<b>C13</b>	K115
N8	C13	Kl9		ив			1			
N 9	M8/Cl0	K20		N 9	M15/C10	K68	1	N 9	M22/C10	K116
NIO	cli	K21		NIO	C11	K69	1	NIO	C11	K117
NII	C12	K22		Nll	C12	K70	l	Nll	C12	K118
							Ì	N12	C13	K119
N12	C13	K23		N12	C13	K71	l		M20/027	
N29	M6/C27	K36		N29	M13/027	K84	}	N29		K132
N30	C28	K37	i	N30	, <b>C</b> 28	K85	1	N30	€28	K133
N31	<b>C</b> 29	к38		N31	<b>c</b> 29	K86	•	N31	` <b>c</b> 29	K134
					030	K87		N32	<b>C3</b> 0	K135
N32	<b>C</b> 30	K39		N32			}			
N333	M7/C27	K40		N33	M14/C27	K88		и33	M21/C27	K136
N34	C28	K41		N34	° 0 <sub>2</sub> 8	K89	İ	N34	<b>C</b> 28	K137
	C29	K42		N35	<b>c</b> 59	K90		N35	.029	K138
N35			1						<b>C</b> 30	к139
N36	<b>c</b> 30	K43	1	N36	<b>C</b> 30	K91		N36		
N37	M8/027	K44	ļ	1137	M15/C27	K92		N37	M22/027	<b>-</b> .
N38	C28	K45		N38	<b>c</b> 28	K93		N38	C28	-
			į		C29	K94		N39	<b>C</b> 29	_
N39	C29	K46		N39						1
N40	<b>c</b> 30	K47		N40	030	Ko5		N40	<b>c</b> 30	

C: Component side

N : Non-component side

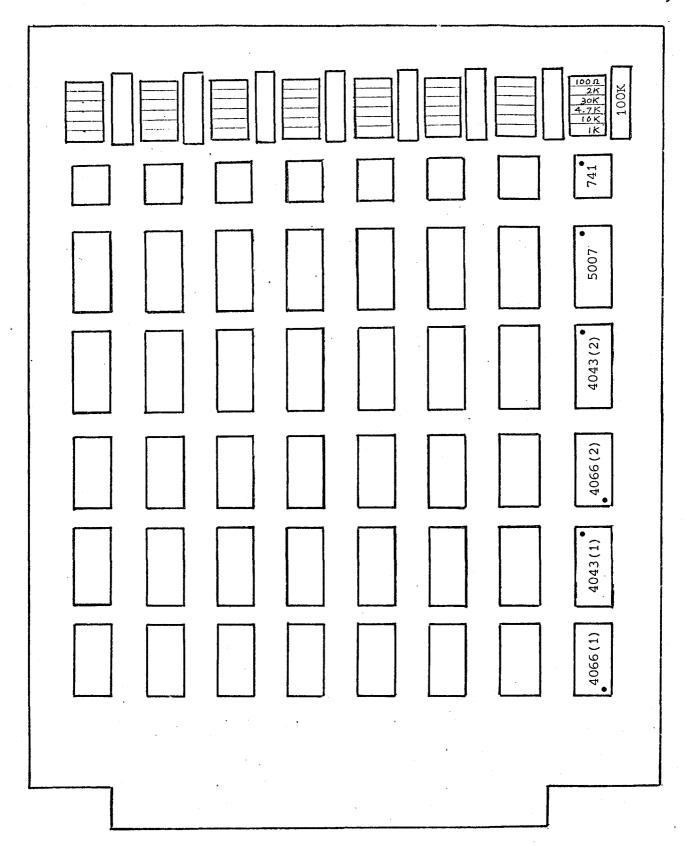


Fig. 20a Memory board, M2 to M22; 18 boards identical. (Component side).

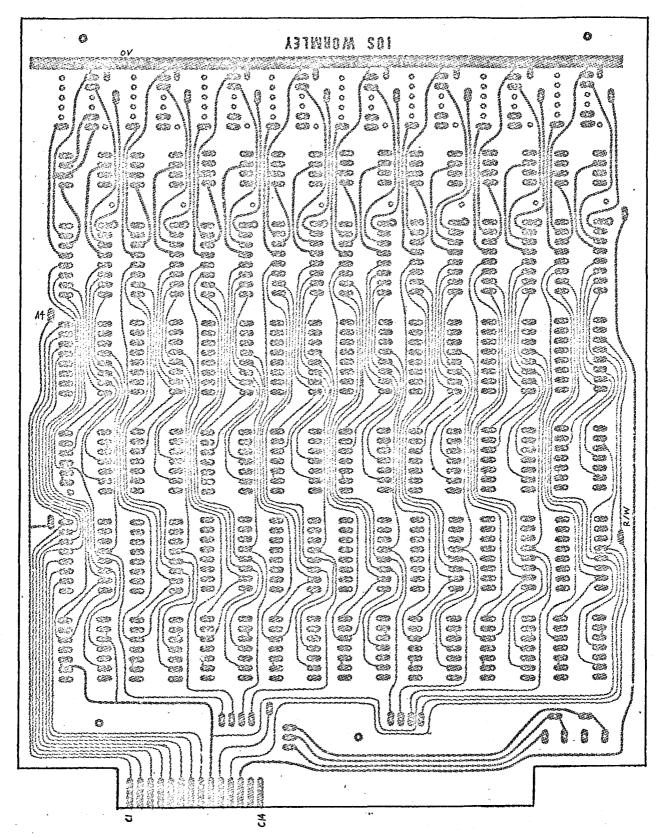


Fig. 20b Memory board, M2 to M22; 18 boards identical. (Conductors on the component side).

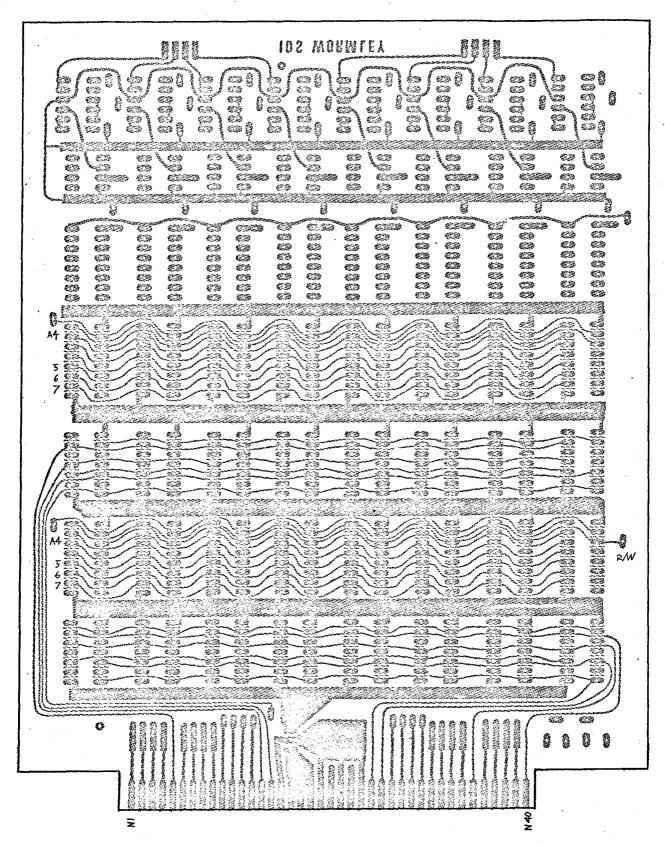


Fig. 20c Memory board, M2 to M22; 18 boards identical. (Non-component side).

Table 6 Connections of the 18 memory boards.

One of the 18 boards, pin No.	Connect-	Function
N1 N2 N3		Output
N4 N5	D8 (LSB)	Data Bus
N-6		<i>1</i> 00 00 100 100 100 100 100 100 100 100
и7 8 и'9		Output
N10	K1	
N 11 N 12	K2 K3	Selector
N.1.3	K.4	
N14 N15	D7 D5	Data Bus
N 16	GN130/9	Ο <b>Λ</b> ··
N 17 N 18 N 19	CN130/1	+5₹
N 20	CN130/9	OA
N 21	CN130/17	
N 22	1	04
N 23	CN130/20	OA +TSA
N 24 N 25	CN130/9	04
N 26	D3	Data Bus
N 27	K5	
и 28	K6 .	Selector
N 29 N_30	K7 K8	l .
N31	NO.	
N32	<u> </u> 	Output
N33		ou opa v
N34		<u> </u>
N35	D1	Data Bus
N36 N37		
N38		Output
N39		
N40	D2	Data Bus
C1	A4	
C2 C3	A3 A2	
C4	ÃÎ.	Address Bus
<b>C</b> 5	OA	aua
C6	A5	
07	A6 A7	
	M1./C28	SW
C10	D6	Data Bus
Cll	M1/C31	R/W
C15	CN130/9	OV VTH

The 18 board, M2, M3, M4, M6, M7, M8, M9, M10, M11, M13, M14, M15, M16, M17, M18, M20, M21 and M22 are identical.

A pin No. whose function only is shown in this table can be determined by other tables:-

Output Table	8
Selector Table	5
Data Bus Table	4, 7
Address Bus Table	4

# Table 7 Connections of the rear panel.

CN103 (socket) From Tape-reader

		7 Fion Tape-Teader
CH103		Connetion
pin No	<u> </u>	
1 1	Bn.	Tape out 1
2	R	2
3	Or	3
4	Y	4
5	Gn	2 3 4 5 6
1 2 3 4 5 6 7 8	Ве	6
7	٧	7 8
8	Gy	8
9	¥	BD30/29 FH
10	R/Gn	BD30/23 TFW
11	R/Be	/25 TBW
12	Y/Be	/27 Clutch
13		Common
14	Bn	Data Bus: 1
15	R	·· 2
16	Or	3
17	Y	2 3 4
. 18	Gn	5 <sub>2</sub> 6
19	Ве	6
20	٧	7
21	Су	8
22		
23	Not .	neeq
24		
25		
<b></b>		

4 co-ax connectors

•		
		Connection
SEQ R-CL	Or/3k	M1/020
SYNC OUT	Or/Be	M1/N38
RND CIK	R	M1/U2
PRINT OUT	Y/R	M1/C26

CN130 (socket) From Power supply

Pin No		Connection
1 to 8	Bk	+5V
9 to 16 18, 19	Gn	OA
17	Ве	-12V
20	R	+12V

"CN133 (socket) To Test unit

-55 (-5						
Pin No		Connection				
1	Y	11/020	R-CIK			
2	Bk	CN133/1	+51			
3	Gn	/9	Ó۷			
4	Be	/17	-12V			
5	R	/20	+12 <b>V</b>			

SEQ/RND switch

Switch pin No	1	Connection
1	Bn	M1/C17
2	R	(RP) RED Clock
3	Or	M1/C23
4	Y	M1/C29
4 5	Gn	M1/C26
6	Be	M1/C24
7, 10	Bk	C11130/1 +5V
8	v	M1/C25
9	Gу	M1/C19
11	Gn/Bk	CN130/9 OV
12	W	M1/C18

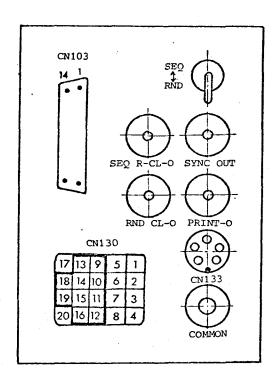


Fig. 21 Rear panel.

	···			,										,							,	
22	21	20	19	18	17	16	15	14	13	12	11	10	9	. 8	7	6	5	4	3	2	Ml	← BOARD NO.
116	112	108	<u>-</u>	104	100	96	68	64	60		56	52	48	20	16	12		8	4	0		
117	113	109		105	101	97	69	65	61		57	53	49	21	17	13		9	5	1		•
118	114	110		106	102	98	70	66	62		58	54	50	10	18	14		10	6	2		- CHANNET NO
119	115	111		107	103	99	71	67	63		59	55	51	11	19	15		11	7	3		CHANNEL NO.
128	124	120		140	136	132	80	71.	72		92	88	84	32	28	24		44	40	36		
129		121			137		81	77	73		93	89	85	33	29	25		45	41	37		
130		122		142			82	78	74		94	90	86	34	30	26		46	42	38		
131		123		143			83	79	75		95	91	87	35	31	27		47	43	39		
								М	ONIT	OR GE	ROUP 1		PIN	NO.	= CH	IANNEI	L NO.		0	50	1 18 34	MONITOR GROUP NO.  PIN NO.

Fig. 22 Position of each channel, shown by the channel number, seen on the front of the memory cabinet without the cover (top); and the output monitor terminals (bottom).

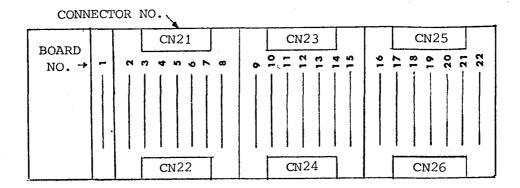


Fig. 23a Rear view of the memory cabinet showing the positions of all the boards and output connectors, CN21 to CN24.

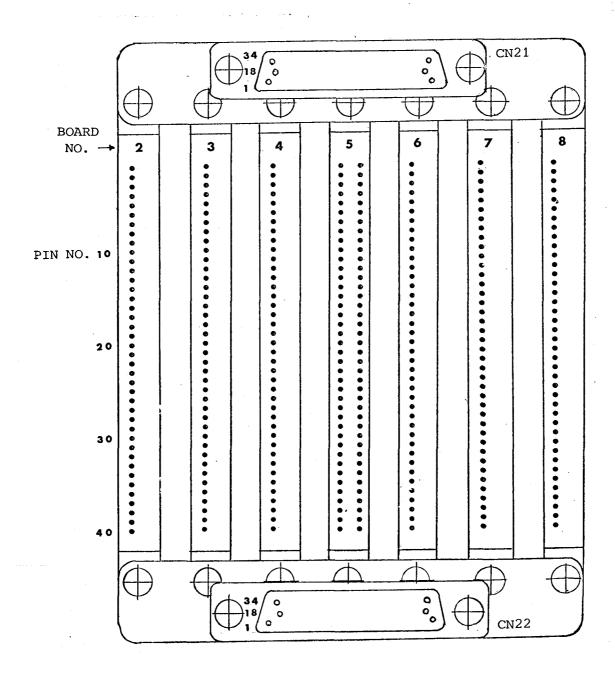


Fig. 23b Details of one third of Fig. 23a showing the pin numbers of connectors (full scale).

Table 8 Relationships between the memory channel numbers, board pins, output connections, and monitor pin numbers.

Memory	From	То	Connector	Monitor
channel	board	connector	wire colour	pin No.
0	150 /01 0	CN21/1-2	Bn-R	(100) 40
0	M2/C1-2 C3-4	3.4	Or-Y	(100) 40 (õ) 1
1 2	03-4 06-7	56	Gn-Be	2
2	C8-9)	7-8	V-Gy	3
1 2 3 4	M3/C1-2	18-19	Bn-R	4
F 1	C3-4	20-21	Or-Y	<del>*</del> 5
5	C6-7	22-23	Gn-Be	5 6
7	c8-9	24-25	V-Gy	7
8	M4/C1-2	34-35	Bn-R	8
99	C3-4	36 <b>–</b> 37	Or-Y	9
10	c6-7	38-39	Gn-Be	1ó
11	C8-9:	40-41	V-Gy	11
12	M6/C1-2	10-11	Bk-Bn	12
13	C3-4	12-13	R-Or	13
14	c6-7	14-15	Y-Gn	14
15	c8-9	16-17	Bn-R	15
16	M7/C1-2	26-27	W-Bk	16
17	C3-4	28-29	Bn-R	17
18	C6-7	30-31	Or-Y	18
19	<b>c</b> 8–9	32-33	Gn-Or	19
20	M8/C1-2	43-44	3k-3n	20
21	C3-4	45-46	R-Or	21
22	C6-7	47-48	Y-Gn	22
23	<b>c</b> 8-9	49-50	Y-Gn	23
24	M6/031-32	CN22/10-11	Bk <b>-</b> Bn	24
25	c33-34	12-13	· R-Or	25
26	<b>c</b> 36 <b>–</b> 37	14-15	Y-Gn	26
27	<b>c</b> 38–39	16-17	Bn-R	27
28	M7/031-32	26-27	W-Bk	28
29	<b>c</b> 33 <b>–</b> 34	28-29	Bn-R	29
30	<b>c</b> 36 <b>–</b> 37	30-31	Or-Y	30
31	<b>c</b> 38 <b>–</b> 39	32-33	Gn-Or	31
32	M8/C31-32	43-44	Bk-Bn	32
33	<b>c</b> 33 <b>-</b> 34	45-46	R-Or	33
34	<b>c</b> 36 <b>–</b> 37	47-48	Y-Gn	34
35	<b>c</b> 38 <b>-</b> 39	49-50	Y-Cn	35
36	M2/C31-32	1-2	Bn-R	36
37	C33-34	3-4	Or-Y	37
38	036-37	5-6	Gn-Be	38
39	C38-39:	7-8	V-Gy	39
40	M3/C31-32	18-19	Bn-R	40
41	033-34	20-21	Or-Y	41 42
42	C36-37	<b>22–23</b>	Gn-Be	43
43	<u> </u>	24-25	V-Gy	43
44	M4/C31-32	34-35 36 37	Bn-R	44 45
45	. 033-34	36 <b>-</b> 37	Or-Y	45 46
46	C36-37	38 <b>–</b> 39	Gn-Be V-Gy	47
47	<b>c</b> 38 <b>-</b> 39	40-41	v-u,y	41

Memory	From	То	Connector	Monitor
channel	board	connector	wire colour	pin No.
No.	Jouru			1
48	и9/с1-2	CN23/1-2	Bn-R	(0) 48
49	C3-4	3-4	Or-Y	49
56	C6-7	56	Gn-Be	50
51	c8-9	7-8	V-Gy	(50) 1
52	N10/C1-2	18-19	Bn-R	(50) 1
53	03-4	20-21	Or-Y	3
53 54	C6-7	<b>22-</b> 23	Gn-Be	<b>l</b> 4
55	c8-9	24-25	<b>V</b> Gy	3 4 5 6
56	M11/C1-2	34-35	Bn-R	
	C3-4	36-37	Or-Y	7 8
57 58	c6-7	38-39	Gn-Be	8
59	C8-9i	40-41	VGy	9
60	M13/C1-2	10-11	BkBn	10
61).	C3-4	12-13	R-Or	11
- 62	C6-7	14-15	Y-Gn	12
63,	c8-9	16-17	Bn-R	· 13
64	M14/C1-2	26-27	W-Bk	14
65	°C3–4	28-29	Bn-R	15
66	C67	30-31	Or-Y	16
67	c7-8	32~33	Gn-Or	17
68	M15/C1-2	4344	Bk <b>–</b> Bn	18
69	c3-4	45-46	R-Or	19
70	C7-7	47-48	Y-Gn	20
71	<b>c</b> 8-9	49-50	Y-Gn	21
72	M13/C31-32	CN24/10-11	Pk-Bn	22
73	<b>c</b> 33 <b>–</b> 34	12-13	R-Or	23
74	<b>c</b> 36 <b>–</b> 37	15–16	Y-Gn	24
75	038-39	16-17	Bn <b>-</b> R	25
76	M14/C31-32	26-27	· W-Bk	26
77	C33-34	28–29	Bn <b>-</b> R	27
78	c36-37	30-31	Or-Y	28
79	<b>c</b> 38 <b>-</b> 39	32-33	Gn-Or	29
80	M15/C31-32	43-44	Bk <b>–</b> Bn	30
81	c33-34	45-46	R-Or	31
82	<b>c</b> 36 <b>–</b> 37	47-48	Y-Gn	32
83	<b>c</b> 38 <b>–</b> 39	49-50	Y-Gn	33
84.	M9/C31-32	1-2	Bn-R	34
85	c33-34	3-4	Or-Y	35
86	<b>c</b> 36 <b>–</b> 37	5–6	Gn-Be	36
87	<b>c</b> 38 <b>–</b> 39	7-8	<b>V</b> G <b>y</b> ·	37
88	M10/C31-32	18-19	Bn-R	38
89	033-34	20-21	Or-Y	39
90	c36-37	22-23	Gn-Be	40
91.	<b>c</b> 38 <b>-</b> 39	24-25	∇-Су	. 41
92	M11/031-32	34-35	Bn-R	42
93	C33-34	36-37	Or-Y	43
94	c36-37	38–39	Gn-Be	44
95	<b>c</b> 38 <b>-</b> 39	40-41	V-Gy	45

	<del></del>		<del></del>	<del></del>
Memory		То	Connector	Monitor
channel	board	connector	wire colour	pin No.
No.	Dour			
26	112 ( /02 0	0705/2 0	Bn-R	(50) 46
96	M16/C1-2	CN25/1-2	1	
97	03-4	3-4	Cr-Y	47
98	C6-7	5-6	Gn-Be	48
99	c8-9	7-8	Ү-Су	49 50
100	M17/C1-2	18-19	Bn-R	(200) 30
101	C3-4	20-21	Or-Y	(100) 1
102	c6-8	22-23	Gn-Be	
1.03	<u>c8-9</u> '	24-25	V-Cy	3
104	M18/C1-2	34-35	Bn-R	4 5 6
105	<b>C</b> 3-4	36-37	Or-Y	2
106	c6 <del></del> 7	38-39	Gn-Be	0
3.07	c8 <b>-</b> 9	40-41	V-Gy	7 8
108	MSO\CJ-5	10-11	Bk-Bn	
109	<b>c</b> 3 <b>–</b> 4	12-13	R-Or	9
1.10	c6 <b>-</b> 7	14-15	Y-Gn	10
111	<b>c</b> 8 <b>-</b> 9	16-17	Bn-R	11
112	M21/C1-2	26-27	W-Bk	12
113	c3 <b>-</b> 4	<b>28–</b> 29	Bn-R	13
114	c6-7	30-31	Or-Y	14
115	<b>c</b> 8 <b>-</b> 9	32-33	Gn-Or	15
116	M22/C1-2	43-44	Bk <b>-</b> Bn	16
117	°C34	45-46	R-Or	17
118	c6-7	<b>47-</b> 48	Y-Gn	18
119	c8-9	49-50	Y-Gn	• 19
120	M20/031-32	CN26/10-11	Bk <b>-</b> Bn	20
121	c33-34	12-13	R-Or	21
122	C36-37	14-15	Y-Gn	22
123	· .038–39	16-17	Bn-R	23
124	1121/031-32	26-27	W-Bk	24
125	c33-34	28-29	• Bn-R	25
126	036-37	30-31	Or-Y	26
127	038-39	32-33	Gn-Or	27
128	M22/C31-32	43-44	Bk-Bn	28
129	c33-34	4546	R-Or	29
130	c36-37	47-48	YGn	30
131	C49-50	49-50	· Y-Gn	31
132	M16/031-32	1-2	· Bn-R	32
133	¢33-34	3–4	Or-Y	33
134	c36-37	56	Gn-Be	34
135	038-39	7-8	<b>V-</b> Cy	35
136	M17/C31-32	18-19	Bn-R	36
137	c33-34	20-21	Or <b>-</b> Y	37
138	c36-37	22-23	Gn-Be	38
139	<b>c</b> 38-39	24-25	V-Gy	. 39
140	M18/C31-32	34-35	Bn-R	40
141	C33-34	36-37	Or-Y	41
142	<b>c</b> 36 <b>–</b> 37	38-39	Gn-Be	42
143	<b>c</b> 38 <b>–</b> 39	40-41	V-Gy	43
143	0,0-07	40-41		-10

Green Gn: Y: Yellow Orange Red Or: Bn: Brown R: Black Bk: White W: Blue V: Violet Gy: Grey Be: Component-side of a board C: Memory board М:

This table should be read, for example, as:Memory channel No. 137 (a group of wires) comes from memory board M17,
Pins 33 and 34; and goes to connector CN26, Pins 20 and 21. The
colours of the wires are Orange and Yellow. This channel output can
be monitored through Monitor Group 100, Pin 37.

### 6. TESTS AND ADJUSTMENTS

Since the input memory system has about 286K bits of memory cells, these have to be tested in an efficient way. A test method developed for this particular memory system is described in this chapter.

The tests are carried out in the following four stages:-

- 1. Test of each memory board;
- 2. Test of the whole system in sequential write mode 2;
- 3. Test of the whole system in sequential write mode 1; and
- 4. Test of the whole system in the random write/read mode.

For each stage of the test, a special test tape is required. Only when 1 is successful, can 2 be successful. Only when 2 is successful, can 3 be successful, and so on. It is recommended, therefore, that the tests be carried out in this order. For 1, a test unit has been designed. For 2, 3 and 4, no special equipment is required, other than a conventional CRO and printer (or tape-punch) which are parts of the model system.

If  $\underline{1}$  is successful, but  $\underline{2}$ ,  $\underline{3}$  or  $\underline{4}$  is not successful, this shows that a fault (or faults) lies in the control circuit (M1, M5, M12, M19) or wirings in the memory cabinet. A guide to finding possible faults can be found in 7.4.

### 6.1 Memory test unit

Fig. 24 shows the memory test unit by which each memory board (M2, M3, M4, M6, M7, M8, M9, M10, M11, M13, M14, M15, M16, M17, M18, M20, M21 or M22) can be tested separately. The test unit has a circuit based on the same principle as that used for the control circuit in the memory cabinet, but with a much simpler construction. The test unit can be operated independently from the memory cabinet, providing it is connected to the cabinet through connector CN133 (power supply and clock), and to the tape-reader through connector CN103 (data input and tape-reader control signals).

By using this test unit, with a test tape, all the 8 channels of memory on each board can be tested simultaneously. The output of each channel can be observed on a CRO, a normal state of operation being shown by a straight sloped line.

Fig. 25 shows the circuit diagram of the test unit. This consists of a tape-control circuit, write/read circuit, and address-code generator.

Tape-control circuit When a manual start switch is activated, a pulse (constant width) is generated by 121(3). This pulse holds the output of FF (00/1 to 6) low, and starts the motor of the tape-reader. When the tape-reader runs, a start code on the tape, '255', is detected by an 8-input NAND gate, 30. This pulse enters 93(3) through 121(2), but this is ignored by the former since 93(3) responds to every two input pulses. When the tape comes to the end, the end signal, also '255', is again generated by 30, and again enters 93(3). This time, 30 activates another pulse to raise the output of the FF, so that the tape stops.

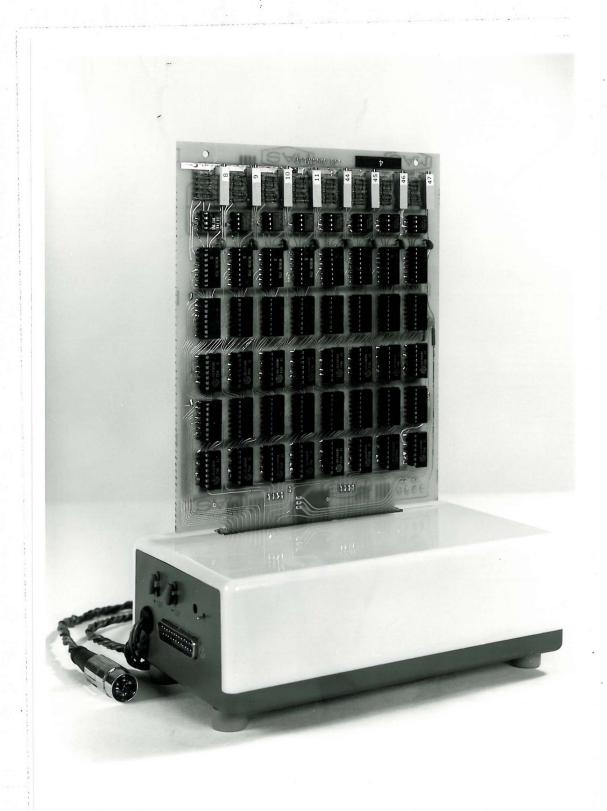


Fig. 24 Memory test unit with a memory board under test.

Write/read signal circuit The output of 93(3) is lowered only for a period between the above two '255' signals. This output voltage controls switch 51 by which a write clock or read clock is selected. Also an inverted output of 93(3) is fed into the board under test, and this controls the electronic switches on the board. The write or read clock passed through 51 is used, after shaping by 121(1), or read clock passed through 51 is used, after shaping by 121(1), for the address code generator. The same pulses are delayed by a delay circuit, 04/1 to 6, and these pulses are used for the CE (chip enable) signal.

Address-code generator This consists of two binary-code ICs, 93(1) and 93(2). The positive-going pulse output of 121(2) is used to reset the address-code generator, so that the start of the binary code is synchronized with the start of the tape codes.

Fig. 26 shows the circuit board of the test unit. Table 9 shows the connections within the test unit.

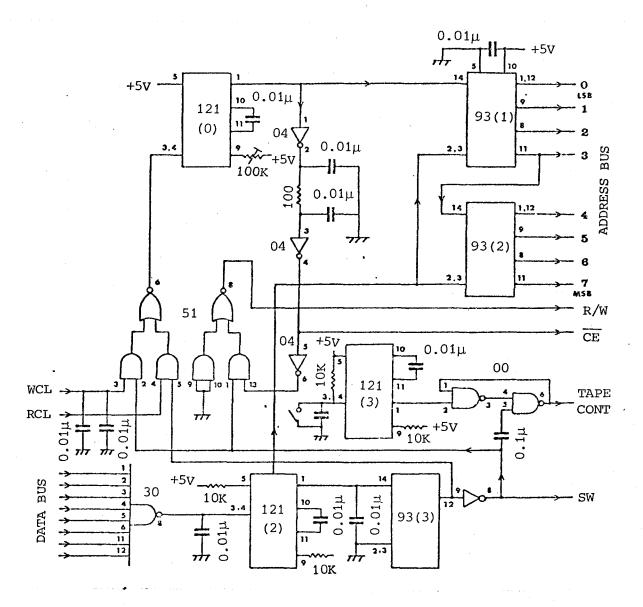
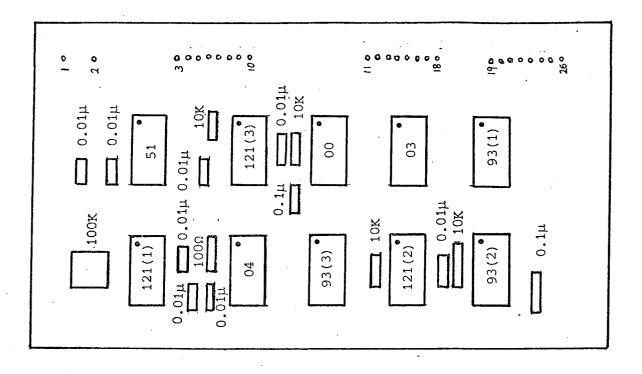


Fig. 25 Circuit diagram of the memory test unit.



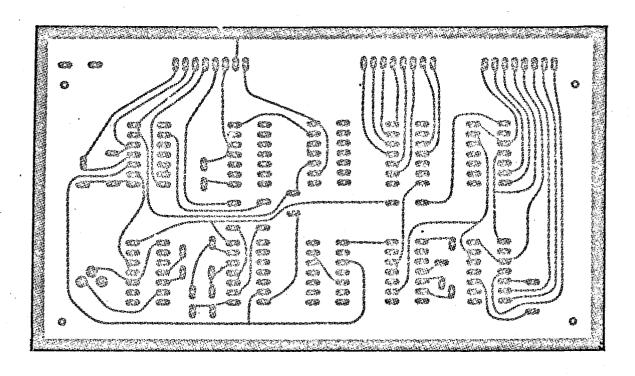


Fig. 26 Circuit board of the memory test unit.

Top: Component side. Bottom: Non-component side.

Table 9 Connections of the memory test unit.

* _		•	•
Test-unit circuit board pin No.	Wire colour	Connection	Function
1 2 3 4 5 6	Gn Bk W/Or W W Bk	CN133/3 CN133/2 CN133/1 CN103/9 CNT/C9 CNT/C11	OV +5V R-CLK W-CLK SW R/W
	W/Or	CNT/C10 C11 C12 C13 C27 C28 C29 C30	CE
8	٧	Micro SW	Start
9	Gn	Micro SW	
10	Or/R	CN103/10	Tape- control
11 12 13 14 15 16 17	Gy V Be Gn Y Or R Bn	CN103/1 & CNT/N35 2 N40 3 N26 4 N25 5 N27 6 N28 7 N29 8 N30	Data 1 2 3 4 5 6 7 8 Addr. 0
19 20 21 22 23 24 25	R Bn Or Y Gn Be	CNT/C5 C4 C3 C2 C1 C6	Addr. 0 1 2 3 4 5 6
26	Су	C8	7

Connector CNT pin No.	Wire colour	C onnection	Function
N16 N17	Gn	CN133/3	OA
N18 N19	Bk	CN133/2	+101
N20	Gn	CN133/3	VO
N21	R	CN133/5	+12V*
N22	Un	cm33/3	ΟV
N23	Be	CN133/4	-12/*
N24	Gn	CN133/3	OA

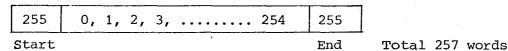
<sup>\*</sup>Through the current-mesuring terminals.

## 6.2 Test tapes

Five different test tapes are required for testing all the modes of the input memory system. Although 8-track punched tapes are used in these examples, other types of tapes can be used, providing they have the same formats as the examples and a suitable tape-reader is used.

The natural binary code is used for the actual test tapes. However, for simplicity, decimal figures are used to describe the formats of the tapes in this chapter. For example, binary '11111111' is represented by decimal '255'.

# Test tape TEMB2



This tape is used for testing each memory board separately. The tape should be formed in an endless loop, with a space of about 100 words. This tape can be run in either direction.

## Test tape TWM1

255	0, 254	1, 253	2, 252	• • • •	254, 0	255
Start	72 times	72 times	72 times		72 times	End
				1	Total 36722	words

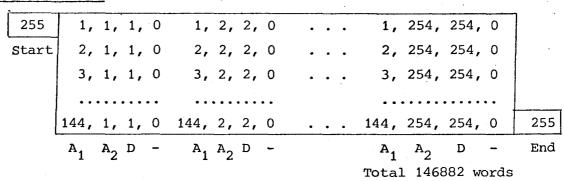
This tape is used for testing the whole system in write mode 1. The margins are the same as above.

### Test tape TWM2

(						
255	0, 1, 2, 3,	254	255			
Start	144	times	End	Total	36722	W

This tape is used for testing the whole memory system in sequential write mode 2. Appropriate margins should be added before the 'Start' and after the 'End'.

### Test tape TRNDW



This tape is used for testing the whole memory system in the random write mode. All the figures (words) from the 'Start' to 'End' should be punched continuously on a single tape. The figures in row A1 represent 'group-addresses' (from 1 to 144), and those in row A2 'addresses' in each set of memory packages (from 1 to 254). The figures in row D represent data (from 1 to 254). The row (-) represents spaces. The margins of the tape are the same as for TWM1.

## Test tape TRNDR

The format of this tape is the same as test tape TRNDW, but all the figures in row D are zero. This tape is used for reading the whole memory which is written by test tape TRNDW.

## 6.3 Test of each memory board

This test is applicable only to each of the memory boards, M2, M3, M4, M7, M8, M9, M11, M13, M14, M15, M16, M17, M18, M20, M21 and M22. The test should be carried out by using the memory test unit (chapter 6.2) so that the rest of the system is not involved.

Before connecting a memory board to any active circuit, confirm the following resistances:-

+5V supply line approx.

-12V supply line approx.

+12V supply line approx.

where each value is referred to a resistance between each supply line on a memory board and its common line. Also each resistance value shown is for a case where a resistance-measuring current flows from the common line to each supply line. Note, the value is directional due to semiconductor circuits.

Test each memory board by using the memory test unit with test tape TEMB2. All 8 channels of each memory board will be written simultaneously. The output of each channel can be observed, through its 5007/4, using a CRO.

After the perfect operation of all the channels is confirmed by running test tape TEMB2 in a certain direction, reconfirm all the channels by running the tape in the other direction. In this way, all the bits of the memory can be examined. Note, bits in two series of natural binary code, 1 through 254, and 254 through 1, are reciprocal.

The correct waveform should be as shown in Fig. 27a or Fig. 27b, depending on the direction of running the test tape. If only a few particular values in a particular channel deviate from the straight slope line of a waveform, as shown in Fig. , this suggests a faulty memory IC. In this case, the replacement of the IC is the only solution. See Appendix 4 and 'Abnormal waveforms' in chapter 6.4, for other types of fault.

h

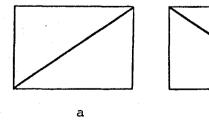


Fig. 27 Normal waveforms

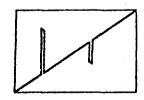


Fig. 28 Waveform suggesting a faulty memory.

### 6.4 Test of the system through the analogue waveforms

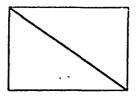
After the performance of each memory board has been confirmed by the previous test (6.3), a performance of the whole system (which is totally digital) in all the sequential modes can be confirmed rapidly by observing the analogue waveforms on a CRO from a DAC which is built in each channel of the memory. Each waveform is available from two different terminals:-

- A Pin 4 of each DAC (5007) with the maximum voltage of 0.4V, and
- $\underline{\underline{B}}$  Monitor terminal on the front panel with the maximum voltage of 0.04V in a reverse polarity to A.

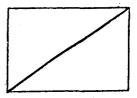
Note,  $\underline{B}$  is available only when the outputs of the channels (CN21 to CN26 in the rear of the memory cabinet) are connected to their loads (LEDs in the main computation circuit, or external resistors of zero to about 1K ohms).

### Normal waveforms

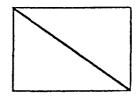
Fig. 29 shows normal waveforms at  $\underline{A}$  when the two test tapes are used. Note, if a test tape is run in a reverse direction, the slope in each figure will be reversed. However, it is <u>not</u> necessary to test the memory by running the test tapes in two directions, if the memory has already been tested by test tape TEMB2 in two directions.



Channels 0, 2, 4 ... 254 with test tape TWM1



Channels 1, 3, 5 ... 253 with test tape TWM1



Any channel with test tape TWM2

Fig. 29 Normal waveforms of ADC outputs with test tapes.

### Abnormal waveforms

If the waveforms of the outputs of the system are not as shown in Fig. 29, there is a fault (or faults) in the system. Fig. 30 shows some examples of abnormal waveforms, with suggestions of possible faulty operations.

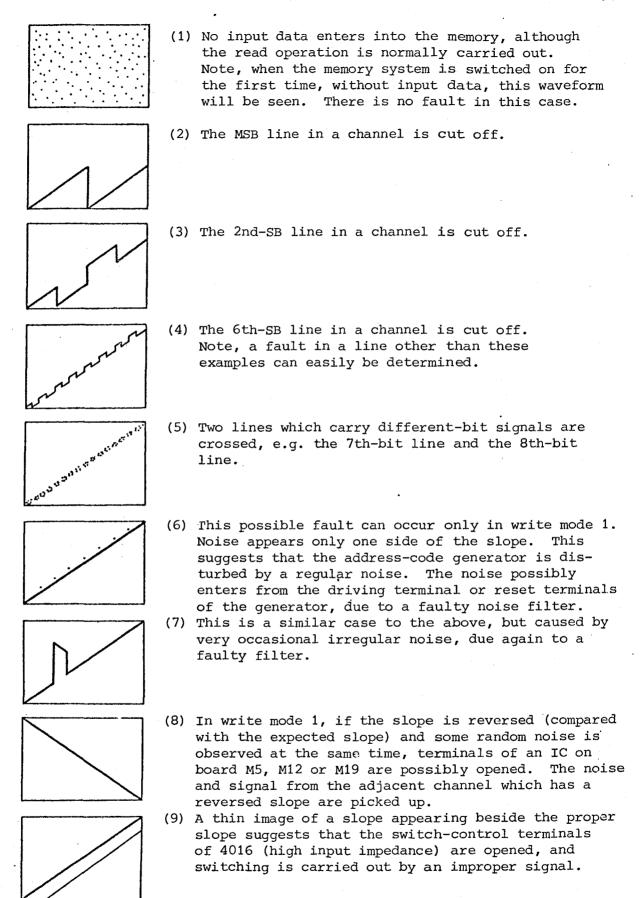


Fig. 30 Abnormal waveforms.

## 6.5 Test of digital circuits in sequential modes

If the test described in chapter 6.4 is satisfactory, this proves the perfect performance of all the digital circuits in the system, except for a few circuits which are solely used for the random read/write mode. In this case, no further test is required for the digital circuits for sequential modes.

If the test of each memory board (chapter 4.3) is satisfactory, but the test of the whole system (chapter 4.4) is not satisfactory, then a fault (or faults) is suspected in the digital circuits of the system. See 'Abnormal waveforms' in chapter 4.4 and 'Guide to fault finding' in Appendix 4, for determining the type of fault and the location of the faulty circuit. Then compare the observed waveform against the correct waveforms shown in Tables 10 through 14.

Table 10 Waveforms in the tape-control circuit and CSW-signal generator in control circuit board M1.

Function	Board pin No	10 pin No	Waveforms
Manual START			Arbitary
		121(3)/5 00/1	
		121(3)/6	
	·	∞/6	
START code on tape		30/8	Tape margin before 'START' code
	·	121(2)/1 93(5)/14	
Reset signal RST		121(2)/6	
CSW	<b>C</b> 28	93(5)/12	
		00/11	
CSW		04(1)/8	
Write clock	C22	157(5)/2	uninimum unini
Read clock	C20	157(5)/3	विरुक्तांविक्तिवर्षः ज्यानकाविक्तिवर्षाः = ज्यावकाविक्तावर्
L1 L2 L3	C15 C14 C13	04(1)/6 /10 /12	Three makes
P	C21	32/6	

Table 11 Waveforms in control circuit board M1 in sequential write and read modes.

Function	Board Pin No	IC pin No	Write mode l	Write mode 2	Read mode O
Write clock	•	14/6 157(5)/2	المتات	لتستنا	x
Pulse-width control		121(1)/6 08/10 157(5)/11 157(5)/9		tpus	<b>X</b>
		93(1)/14 93(3)/14	1_1_1	h	town I
A	N29	93(1)/1 157(1)/4			
В	N27	9 7	→  280 P		
C	иля	. '8 , 9			
D	N19	. 11 . 10			
		93(2)/1 157(2)/4	~ 280 Pw -	~ 2"P	~ 5/2P,
		9 7			
		8 9			
		11 12	<u> </u>	1	
	İ	93(3)/1 157(3)/4			
		9 '7	2Pm	,	2Pr
		8 9		!	5/2P,
		10 12			3/2/,
•		1 4 15	i		
		93(4) 8 7 7 14 8 7 7 9 13 8 13			
		8 15 9 8 13 11 12 12			
			→   <- 36Pw		
Jl	W17	42/1	30/2	1 3/2/2	
2	N18	2			•
3	N19	3			· ·
4	N20 N21	4			x
5 6	NST.	5			
7	N23	7			
. 1	N24	83	_		
9	N25	9	<del> </del>	<u> </u>	
L1 L2	C15 C14	04(1)/6 10	I Always	I. Always	2F
13 P	C13 C21	13 32/6		<i>⊃P.,</i>	H Always

 $<sup>\</sup>mathcal{P}_{\omega}$ : Write-clock period.  $\mathcal{P}_{\varepsilon}$ : Read-clock period. X: Irrelevant.

tow : Controlled pulse width.

Table 12 Waveforms in control circuit board M1 in sequential read modes 0 and 1.

Pin No	Board IC p'in No Pin No C20 157(5)/3  121(1)/6 157(5)/10	Read mode O	Read mode 1
C2O			R. Maria participation of the state of the s
	121(1)/6		
	93(3)/14	mbrentantalenata	Pr International trans
N39	N39 93(4)/11	x	
	93(8)/2,3	X	Write Read
	93(8)/12	х	
	14/11	I. Always	
	93(1)/2,3 93(2)/2,3	I Always	
N36 N34 N35 N31 N30	N38	5/2 p	572P,
N36 N34 N35 N31	N36 N34 N35 N31 N30	93(5) 9 8 1 1 1 2 2 1 1 2 2 1 1 1 2 2 1 1 1 2 2 1 1 1 2 2 1 1 2 2 1 1 1 2 2 1 1 1 2 2 1 1 1 2 2 1 1 1 2 2 1 1 1 2 2 1 1 1 2 2 1 1 1 2 2 1 1 1 2 2 1 1 1 2 2 1 1 1 2 2 1 1 1 2 2 1 1 1 2 2 1 1 1 2 2 1 1 1 1 2 2 1	(1) 9 (1) 7 (2) 2/2 (1) 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1

 $P_r$ : Read-clock period. X: Irrelevant.

Waveforms in sub-control circuit board M5 in sequential write and read modes. (M12 and M19 are identical to M5).

Function	Board Pin No	IC pin No	Write mode l	Write mode 2	Read mode O
A	N16	154(1)/23 154(2)/23 154(3)/23	-1/2-2Pw		x
. В	и17	154(1)/22 154(2)/22 154(3)/22		MANAMA	x
C	и18	154(1)/21 154(2)/21 154(3)/21			x
D	N19	154(1)/20 154(2)/20 154(3)/20			<b>x</b> .
P	N22	154(1)/18 154(2)/18 154(3)/18			H Always
* J1	N23	154(1)/19	- 16 Pw	-16Pw	
<b>J</b> 2	N24	154(2)/19			x
<b>J</b> 3	N25	154(3)/19			
				_	2.5
L1	N2 <b>7</b>	04/1,3,5 9,11,13	1 2 Pw	H Always	
* KJ	N2 <b>7</b>	04/1,3,5 9,11,13 08(1)/6			
* K1 K2	N1 N2	08(1)/6 3	III sentrajalisi		
* Kl	Nl	08(1)/6	III sentrajalisi	Always	→  <del> 29,</del>
* K1 K2	N1 N2	08(1)/6 3	III sentrajalisi	Always	
* K1 K2 K3	N1 N2 N3	08(1)/6 3 8	III sentrajalisi	Always	
* K1 K2	N1 N2	08(1)/6 3	2P	Always	
* K1 K2 K3 K45 K46	N1 N2 N3	08(1)/6 3 8 	2P	Always	MINIMAL All the
* K1 K2 K3	N1 N2 N3 C37 C38	08(1)/6 3 8  08(12)/6 3	2P	Always	
* K1 K2 K3 K45 K46 K47	N1 N2 N3 C37 C38 C39	08(1)/6 3 8  08(12)/6 3 8 11 154(1)/1	2P	Always	MINIMAL All the
* K1 K2 K3 K45 K46 K47	N1 N2 N3 C37 C38 C39	08(1)/6 3 8  68(12)/6 3 8 11	2P	Always	MUMILIAN All the
* K1 K2 K3 K45 K46 K47	N1 N2 N3 C37 C38 C39 C40	08(1)/6 3 8  08(12)/6 3 8 11 154(1)/1	2P	Always	MUMILIAN All the
* K1 K2 K3  K45 K46 K47 K48	N1 N2 N3 C37 C38 C39 C40	08(1)/6 3 8 68(12)/6 3 8 11 154(1)/1 2	2P	All the channels	All the channels

Pr: Read-clock period. X: Irrelevant. . P. : Write-clock period.

<sup>\*</sup> For board M12: J4 to J6; K48 to K95 should be applied. For board M19: J7 to J9; K95 to K139 should be applied. \*\* All the waveforms are independent of test tapes.

Table 14 Waveforms in each memory board in sequential write/read modes.

Func- tion	Board Pin No	IC pin No	0	Write mode 1 Tape TWM1	Write mode 2 Tape TVM2	Read mode O
R/W	Cll	9112(1)/14 & 9112(2)/14 in 8 channels			(temminilonianie)	H H
CSW	<b>c</b> 9	4016/5,6,12 4016/5,6,12 in 8 channe	,13; ,13	H Always	H: Always	L Always
KO.	N10		Ch 1		144 Pm	
Kl	Nll	9112(1)/13	2	<u> </u>		2Pr
K2	N12	9112(2)/13	3		NIII .	
К3	N13	in each of these	4		,	In all the
K4	N24	channels	5	<u> </u>		channels
K5	N28	ž	6	<del>                                      </del>		
K6	N29		7	16Py 238Pm	<u> </u>	
K7	N30		8	2388	DINU	
1	N35	4016(2)/1				·
2	<b>N</b> 40	9				
<sub>20</sub> 3	N26	4	the tels			
B 4	N25			As in	As in	x.
Data bus	N15		ell ohanr	tape TWM1	tape TWM2	
A 6	<b>C</b> 10	1	선호			
7	N14	9				
8	<b>N</b> 5	11				:
0	<b>C</b> 5	4 4				
1	C4	3 3		<u> </u>		
م ع ع	<b>c</b> 3	2 2	o n			1
£3	C2	1 N 1	the nels	<u> </u>	572 P.,	572 P,
Address of the contract of the	Cl	(1)2116 5 15 5 5 5 5 5 5 5 5 5 5 5 5 5 5 5 5	all the channels	4		
£ 5	<b>c</b> 6	5   5     5   5	α H α			
₹ 6	<b>C</b> 7	6 6		162 288 Pm		
7	<b>c</b> 8	7 7				
1		10 9 5		, , , , , , , , , , , , , , , , , , , ,	, , , , , , , , , , , ,	
면 2 대		8 2 10 6 8 2 11 7 4 6 1 6 7	nel			
٤ ۾	ted	8 10 6 8 11 7 2 12 8	ıam			
4 14 14 14 14 14 14 14 14 14 14 14 14 14	190	2 12 6 8	o			1
∓ 5 12 5	con	4 12 5 9	each channel	-71400 Pm->	5/2 P>	- 5/2 Pr
r 6	Not connected	<u>ə</u> 2 <u>ə</u> 11 10	H,			
Lines within board o o o o o o	Nc	2010 2010				
H 8		4 8° 9 12	<u> </u>	***************************************		

 $P_w$ : Write-clock period.  $P_r$ : Read-clock period. X: Irrelevant. 18 boards, M2, M3, .... M22 are identical.

## 6.6 Test of the random write/read mode

Keeping all the circuit boards in a normal operating state in the memory cabinet, apply test tape TRNDW for writing the test data. Then apply test tape TRNDR for reading it. The output should be printed in a digital form. The correct output should be as follows:-

1, 2, 3, 4 ...... 254 (repeated in 144 sets)

If the output does not agree with this, a fault (or faults) will be in the circuits which are solely used for the random mode. Compare the observed waveforms in the circuits against the correct waveforms shown in Table 15.

Table 15 Waveforms in control circuit board M1 in the random write/read mode.

·		·		<del></del>
Function	Board Pin No	,IC pin No	Write	Read
Write clock		14/5	e Pw	
Input		93(7)/1		
A		93(7)/12		
В		93(7)/12		The same as in write, but
Sampling A		04(2)/12		period = 2
code B		04(2)/6		, , , , , , , , , , , , , , , , , , ,
F1		08/6		
F2		08/10		
<b>F</b> '3		08/11		·
Input data from tape	Nl to N8	75(1)/3,6,7,2 75(2)/ " 75(3)/ " 75(4)/ " 75(5)/ " 75(6)/ "	A, A2 D	A1 A2
		75(1)/15,10,9,16 75(2)/ "	At L	A. L.
Sampling		75(3)/15,10,9,16 75(4)/ "	A2	As L
		75(5)/15,10,9,16 75(6)/ "	D D	
Delayed & shaped F3	C26	121(4)/1		
RND read clock	·	157(5)/3	X	
Output data	N9 to N16	Data bus	x	

Pw: Write-clock period. P: Read-clock period. X: Irrelevant.

Waveforms for other parts of the circuit are not shown, since they depend on addresses given in a random mode.

The movement of the tape in a random read mode depends on a related external system.

# 6.7 Adjustments

The digital circuits in the input memory system do not require any adjustment, if they work properly. The analogue parts of the system require three types of adjustments only when the system is built for the first time or overhauled.

## (1) Power supply voltages

The three power supply voltages should be adjusted to

+12.0V ± 1%

-12.0V ± 1%

+5.0V ± 2%

## (2) Pulse width of the reading clock

Apply test tape TWM2, and observe the output waveforms of any memory channel through the monitor terminal (on the front panel of the memory cabinet) by a CRO. Generally two lines will be seen on the CRO, one being sloped, and the other one a horizontal line. Adjust the potentiometer, PULSE WIDTH (on the front panel), so that the horizontal line on the CRO cannot be seen, or very thin compared with the sloped line.

Note, the above two lines are part of a single voltage, as shown in Fig. 31, which is a train of pulses. The pulse width,  $t_{pw}$ , depends on the read-clock rate. Since the same pulse-width control circuit is used for the write clock, its pulse width is also controlled at the same time. However, this does not affect the performance of the system.

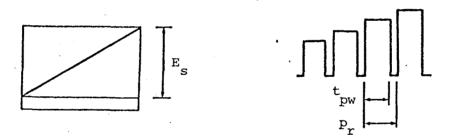


Fig. 31 Output waveform seen on a CRO (left) and its details (right).

### (3) Full scale of each DAC

Each memory channel has a DAC by which a digital signal is finally converted into analogue current. This conversion scale should be adjusted individually.

Apply test tape TWM2, and observe the output waveform through the monitor terminal with a CRO whose sensitivity is calibrated to  $\pm 0.05\%$ . Adjust a potentiometer in each channel (on the edge of each memory board) so that

$$E_{S} = 0.400V \pm 1%$$

where E is the voltage corresponding to the height of the slope shown in Fig. $^{\rm S}$ 31.

Table 16 is a summary of the performance of the input memory system. Fig. 32 shows the constant-current characteristic of the analogue output of one of the memory channels. Fig. 33 shows an example of the output current of a memory channel which was derived from a digital input in write mode 2.

Table 16 Summary of performance of the input memory system

		· ·	<del></del>		
		Form of data	Sequential write mode 1: F <sub>1</sub> (t) <sub>x,y</sub> Sequential write mode 2: F <sub>2</sub> (x,y) <sub>t</sub> Random write/read mode, with addresses		
		Data code	8-bit natural binary code, one word per data, from 0* to 254*		
Input		Address code	8-bit natural binary code 000*-001* to 000*-254* 001*-001* to 001*-245* addresses  143*-001* to 143*-254* in all)		
		Start/end codes	255*		
		Channel	Single parallel 8-bit TTL		
		Write speed	Arbitrary up to 100K words/s Typical sequential mode, 500 words/s		
		Туре	N-channel MOS large-scale ICs		
		Capacity	Capacity 8 bits × 256 increments × 144 channels 294,912 bits in all		
Memory		Max store period	As long as the power supply is maintained		
	[a]	Form of data	Sequential mode 0: F(t) <sub>x,y</sub> repeat continuously Sequential mode 1: F(x,y) <sub>t</sub> repeat with intervals Simultaneous outputs in 144 channels		
	Sequenti	Туре	Analogue currents, signal (±2 mA) max) with a DC bias (8 mA) in each channel which can drive up to 5 optoelectronic couplers		
Output		Read speed	Arbitrary up to 100K words/s (equivalent) Typically 1K words/s (equivalent)		
		Terminals	Floating current output, independent of external load up to 500Ω		
	dom	Read speed	Arbitrary up to 100K words/s		
	Random	Data code	8-bit words		
		Terminal	Single channel 8-bit data bus, TTL logic		
*		Sync signal	TTL logic, between an external apparatus		
		Programmed	Write start, Write end, and Read start		
Control		Manual	Selection: Sequential or Random Write mode 1 or 2 Read mode 0 or 1 Read clock rates Adjustment: Read-clock pulse width Full scale of each analogue output		

	r					
Accuracy	Resolution	0.4% of the full scale				
	Linearity	Better than 0.4%				
	Frequency range of analogue output	This is limited by the IC in each output; DC to 10 kHz (-3 dB) with 747C. The ADC in each channel, DC to 1.8 MHz.				
	Stability	FS temp. coeffic. of the DAC, 10 ppm/°C Power-supply sensitivity of the DAC, +0.0003 FS/%VS				
Temperature range	Operation	0 to +50°C Limited by the power				
	Storage	-55 to +85°C supply units				
Power requirement		240v, 50 Hz, 0.65A rms (156W)				
Protection		Voltage monitor for the +5V line High-voltage shut down (100 ns) 240V AC-line shut down (50 ms) Audible alarm Protection for each power unit				
Dimensions & Weight	Memory cabinet	$50 \times 35 \times 22$ (H) cm <sup>3</sup> , 12.5 Kgr				
	Power cabinet	50 × 35 × 22 (H) cm <sup>3</sup> , 14.0 Kgr				

<sup>\*</sup>Natural binary code is represented by a decimal number for convenience.

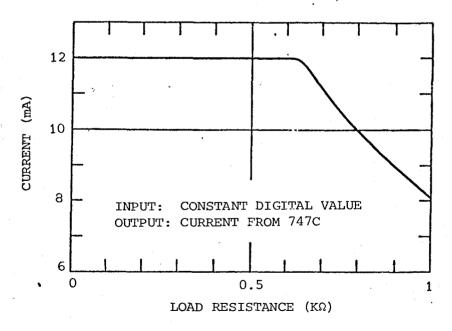


Fig. 32 Constant-current characteristic of the analogue output of a memory channel.

This characteristic shows that the output current is independent of its load up to about  $0.6~\mathrm{K}\Omega$  which is equivalent to about 5 optoelectronic couplers.

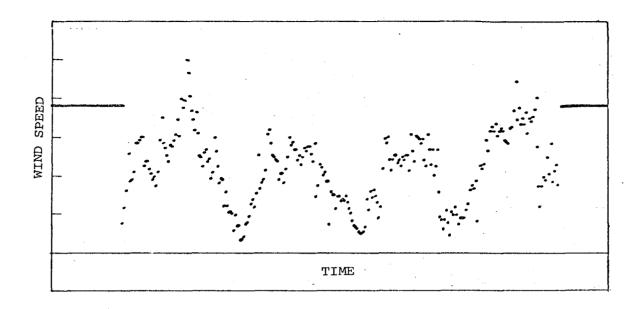


Fig. 33 Example of the wind variation with time, reproduced by the input memory system.

Input: Digital data of hourly-mean wind speed for 10 days.

Input: Digital data of hourly-mean wind speed for 10 days. Output: Analogue current through an optoelectronic coupler

driven by one of the channels of the system.

Intervals = 100µS.

### 8. CONCLUSIONS

A new electronic memory system has been developed by which the electronic model for tides and storm surges can more efficiently be operated with a higher accuracy and longer successive period than the previous memory. The new system can also be used as a general purpose random access memory for handling data relating to the project.

### ACKNOWLEDGEMENTS

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- (2) Ishiguro, S. (1977) Input Memory, IOS Internal Document, pp. 53.

### Appendix 1

#### FORMATS OF INPUT TAPES

The input system has a set of input-data terminals into which any type of input signal can be fed, providing its format satisfies the specifications of the terminals. For simplicity, however, examples given in this appendix are only for punched tapes with a tape reader.

### Sequential modes

An input-data tape for a sequential mode should have the following format:-

- (1) The tape should have 8 tracks;
- (2) A word (or a single value) in the input data should be represented by an 8-bit natural binary code, from 0 to 254 in decimal equivalent;
- (3) '1' in the binary code should be represented in such a way that this produces a logic high signal at the input terminals of the system, and '0' in the reversed state;
- (4) Both the start code and end code are represented by binary '1111 1111' (254 in decimal equivalent). The start code should be put on the tape immediately before the first word of the input data, and the end code immediately after the last word of the input data;
- (5) All the 144 channels of the memory are read simultaneously with a synchronized timing. The order of reading words within each channel depends on the order in which they are written. There are two write modes:-

# Write mode 1

Fig. A1 shows the relationship of the write words and read words. The input data should be written from the top-left to bottom-right continuously. Then the reading will be carried out from the top to bottom within each channel and all the channels simultaneously. The words in the 1st column of Fig. A1 (indicated by 1 to 254) will come out in this order from the output terminal of the 1st channel, the 2nd column from the 2nd channel, and so on.

## Write mode 2

(6) Fig. A2 is similar to Fig. A1, but for write mode 2. The input data should be written again from the top-left to bottom-right continuously. Then the reading will be carried out from the left to right (indicated by 1 to 254) within each channel and all the channels simultaneously. The words in the 1st horizontal line in Fig. will come out in this order at the output terminal of the 1st channel, the 2nd line from the 2nd channel, and so on.

If the use of the full memory is not required, parts of the memory can be left blank. The relationship of write and read of 'blank word' is exactly the same as in (5). However, a certain code should be filled in this position, otherwise a previously written word, or a random noise, can remain in this position of the memory.

	-	·	1	44 channels —			
Start Code	1	1	1		1	1	
	2	2	2	•••••	2	2	
	•	•	•		•	•	
	253	253	253	••••	253	253	
	254	254	254		254	254	End Code

Fig. A1 Format for write mode 1

							_
Start Code	1	2	3		253	254	
	1	2	3	••••••	253	254	
140 channels	•	:	:		•	:	
	1	2	3		253	254	
	1	2	3	• • • • • • • • • • • • • • • • • • • •	253	254	End Code

Fig. A2 Format for write mode 2

Note: The numbers in Figs. A1 and A2 show the order of simultaneous reading, and not input data.

### Random mode

The formats (1) to (4) for the sequential modes can equally be applied to the random mode. In this mode, each word in the input data must be accompanied by an address into which the word is written. Fig. A3 shows the format of one section consisting of two words for (A1 and A2), data (D) and a space (-), where A1 is from 1 to 144, and A2 is from 1 to 254. The order of such sections in the input data does not have to be considered, because each section has an address. The maximum number of the sections is 36576. Note, address 0 and 255 are not used.

The formats by which data in a particular address is read is related to an external system (e.g. a printer). See instruction for each external system.

A <sub>1</sub>	A <sub>2</sub>	D	-

Fig. A3 Format for random write mode.

## Appendix 2

### SIMULATION OF A WRITE MODE

An actual write-mode operation can be completed in a short time (about one minute at the longest, with the optical tape-reader). This is, however, too short for checking various parts of the system in a write mode. In order to simulate a write mode operation for an adequate period for a test, the following procedure should be applied:-

- Make a short tape in an endless loop which has no word. (1)
- (2) Interrupt all the light beams in the tape-reader head a few times by using a piece of paper, so that the system turns into a write mode (this is indicated by the red LED 'ON' on the front panel of the input memory cabinet).
- (3) Apply the endless tape to the tape-reader. Set two of the switches on the tape-reader,
  - and  $3 \rightarrow$ Right side Irrelevant

and

Note, the read mode can be kept for any length of time without any special procedure.

#### OPERATING INSTRUCTIONS

### 1. Preparation

Connect the following 6 connectors:-

CN130 (Memory cabinet) - CN130 (Power-supply cabinet)
CN103 (Memory cabinet) - CN103 (Tape-reader)
CN21 to CN22 (Memory cabinet) - Main computation cabinet

Earth terminal (Memory cabinet) - Earth terminal (Control cabinet)

Power line (Main cabinet) - 240V AC line

CN11 (Tape-reader) - CN11 (Control cabinet)

#### Switch on:-

Power switch (Control cabinet) ... Red light will be ON.

Power switch (Memory cabinet) ... 4 red lights will be ON.

If one of the 4 lights (possibly -12V indicator) does not come ON, try again after switching off for a few seconds.

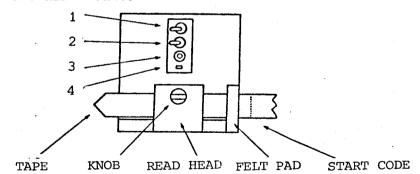
## 2. Selection of operating modes

Select the write mode and read mode required:-

Sequential or random mode switch (on the rear panel)
Write mode 1 or 2 switch (on the front panel)
Read mode 0 or 1 switch (on the front panel)

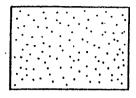
### 3. Starting an input tape

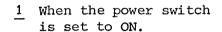
Tape-reader switches should be  $1 \rightarrow \text{Left side}$ ,  $3 \rightarrow \text{Neutral}$ . 2 and 4 are irrelevant.

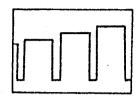


- B The input tape should be wound onto a reel, and the reel should be supported by a holder, so that the tape can be pulled at a speed of about 1.3 m/s. Prepare a large box into which the tape is fed, unless an appropriate take-up reel is available.
- Pass the tape through the <u>felt pad and read head</u>. Position the start code about 10 cm before the read head, and lock the <u>knob</u>.
- Press the <u>red button</u> on the memory cabinet. The tape will run until the <u>end code</u> passes through the <u>read head</u>. Then the tape will stop, and read mode will start automatically.

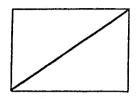
Note If the output of any memory channel is monitored by a CRO, the following patterns can be seen for a correct starting.







During a write mode.



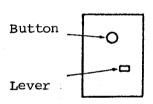
3 After a write mode has been started.

# 4. Protection circuits

In order to protect the memory system from a high voltage, the +5V supply line of the memory is continuously monitored by an electronic circuit. If this voltage is changed accidentally, other dc power supply lines will be shut down within 100 ns. The 240V ac line will be cut off within 50 ms. Then a buzzer will be heard.

If this happens, disconnect the 240V connector from the ac power line, and eliminate the cause of the fault. The protection circuit (located at the rear of the power supply cabinet) can be reset in the following way:-

- 1 Press the lever downwards.
- 2 Press the button.
- 3 Then release the lever.



Note Each power supply unit (+5V, -12V or +12V) has its own protection circuit and a fuse. The 240V connector also has a fuse.

## 5. Random read mode

Since this operation is related to an external system, follow the instructions for each external system.

#### GUIDE TO FAULT FINDING

Most parts of the input memory system are used for both the sequential and random modes, and only minor parts are used for the random mode only. The former can be tested rapidly by using sequential mode test tapes and observing the outputs on a CRO. The latter requires a checking with a numerical printer, but the circuits involve a few components.

If an abnormal waveform is found in a sequential mode test, most types of fault can be analysed by the waveforms shown in Fig. . Although the type of fault itself suggests the location of the faulty circuit, the following considerations also help to find the location.

- (1) If a common type of fault is found throughout all the memory channels, the fault will be in the control circuit.
- (2) If a common type of fault is found throughout a group of 6 memory boards (e.g. M2, M3, M4, M6, M7 and M8), and not in other groups, the fault will be one of the sub-control circuit boards related to this group (e.g. M5).
- (3) If a fault is found in a single memory board only, the fault will be either the board itself or in a circuit of the relevant sub-control board.
- (4) In the case of (1) to (3), the relevant board-connectors and wirings should be checked.
- (5) If a fault is in a memory board, the faulty component can more easily be found by testing this board with the memory test unit.
- (6) In most cases, a board which has a possible fault can be confirmed by replacing this with an identical board. Note, the 18 memory boards, M2, M3 ... M22 are identical; the 3 sub-control boards, M5, M12 and M19 are also identical. Similarly, an IC which has a possible fault can be confirmed by replacing this with an identical type of IC.
- (7) Most faults, other than faulty ICs or wrong wiring, are dry-joints or short-circuits due to imperfect soldering.
- (8) If test tape TEMB2 does not start in a test with the memory test unit, this suggests accidental contact (or contacts) in the data bus, address bus, R/W lines, CE lines or SW lines on the board.

mm

10

d

A simple tool as shown in <u>a</u> has been prepared. Each memory board (M2, M3 etc) has two holes in its upper and lower parts. Use one of them for extracting the board with the tool, as shown in <u>b</u> or <u>c</u>. Each sub-control circuit board (M5, M12 or M19) has a hole for extracting it with the tool. Pull the board as shown in <u>d</u>.

